

The background of the slide features several overlapping, semi-transparent images of organic semiconductor devices and sensors. These include micrographs of thin-film structures with various patterns, such as grids and lines, and close-up views of what appear to be sensor components or electrodes. The images are set against a light green background with a darker green border.

# Dispositivi e sensori a semiconduttore organico

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**1: Semiconduttori organici**

**2: Organic Thin Film Transistors (OTFT)**

**3: Sensori basati sugli OTFT**

# Outline prima parte

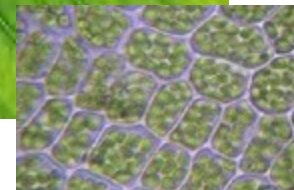
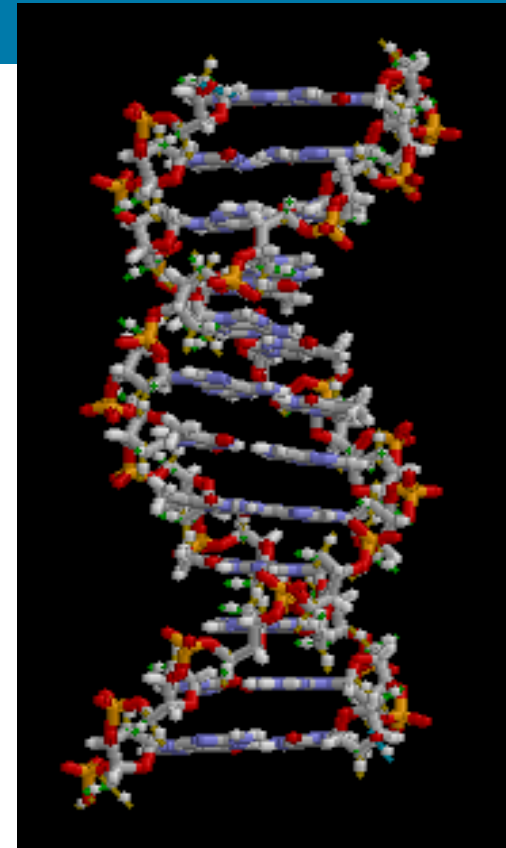
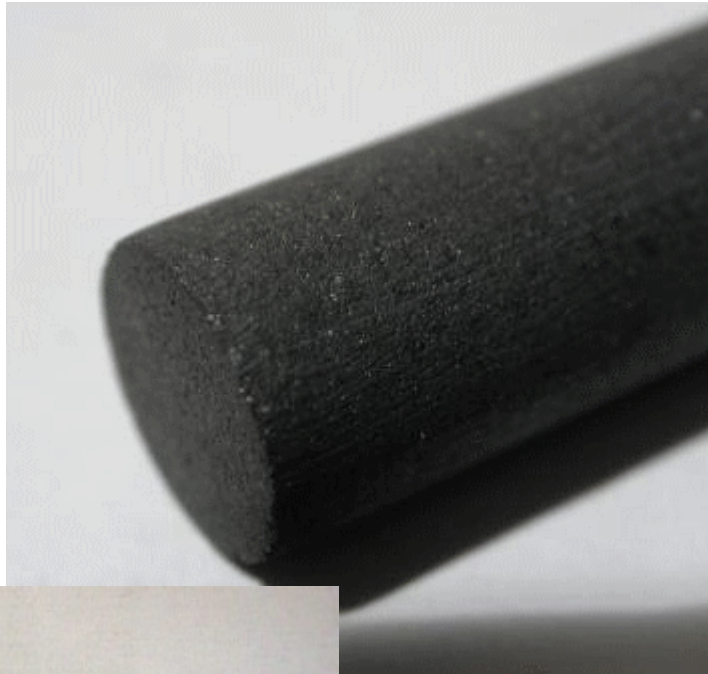
**Proprieta' degli orbitali del Carbonio**

**Molecole coniugate**

**Semiconduttori organici: orbitali molecolari e bandgap**

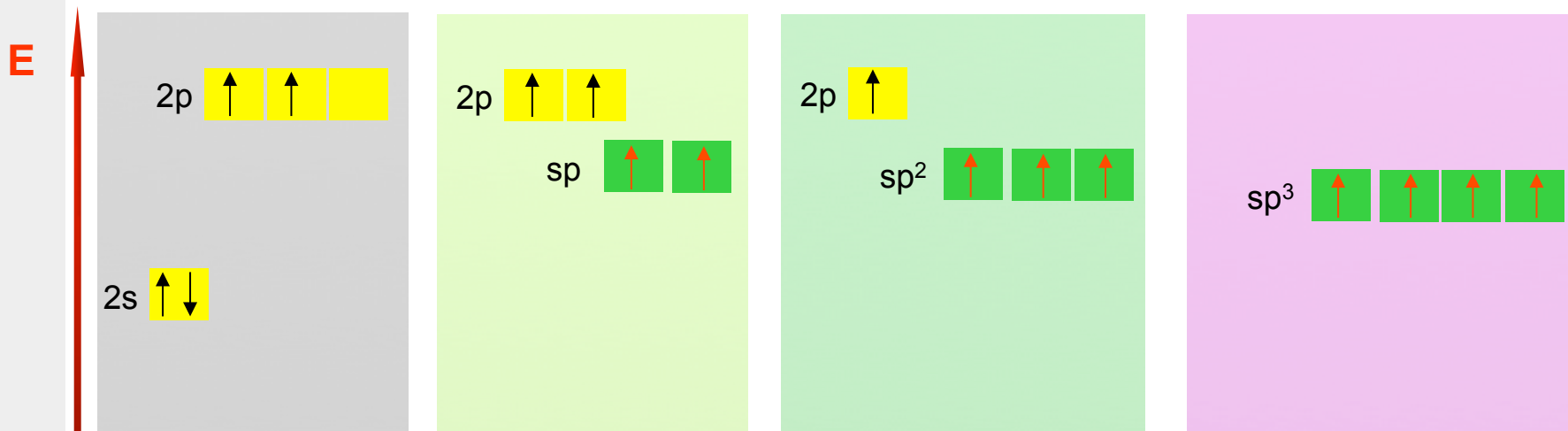
**Portatori di carica e trasporto nei semiconduttori organici**

**Influenza della morfologia sul comportamento elettrico dei film sottili organici**





# Hybridization of orbitals in Carbon

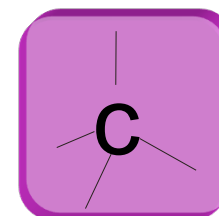
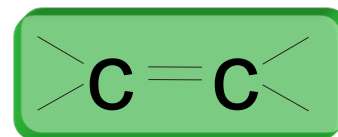
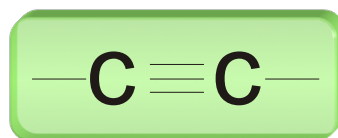


**Fundamental state**

**hybrid sp**

**hybrid sp<sup>2</sup>**

**hybrid sp<sup>3</sup>**



1σ  
2π  
120 pm

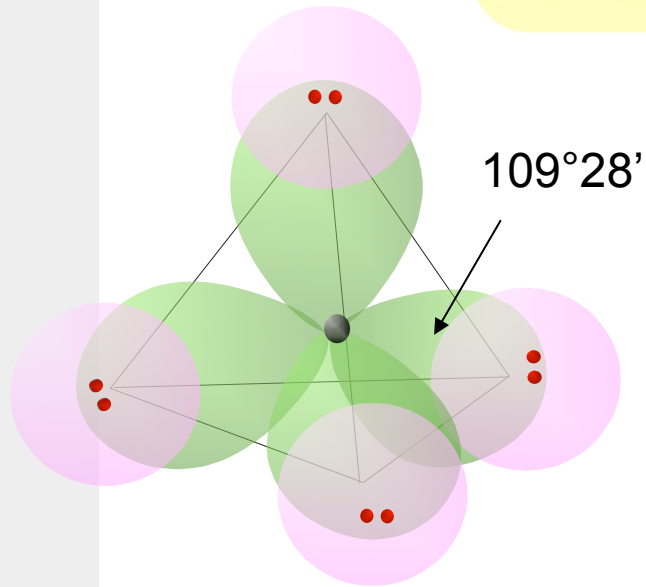
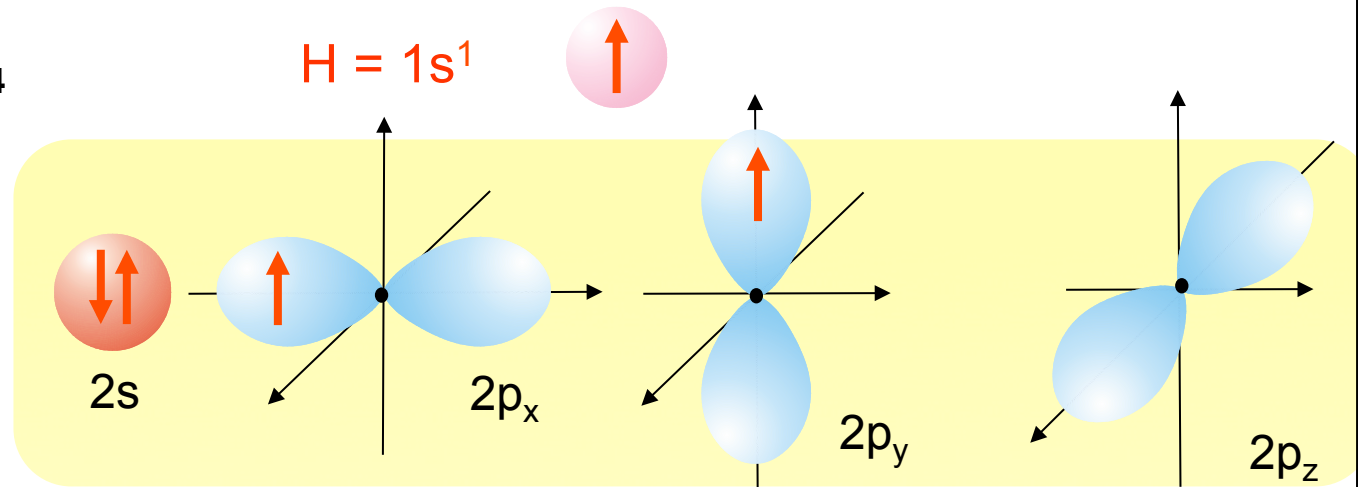
1σ  
1π  
134 pm

1σ  
154 pm

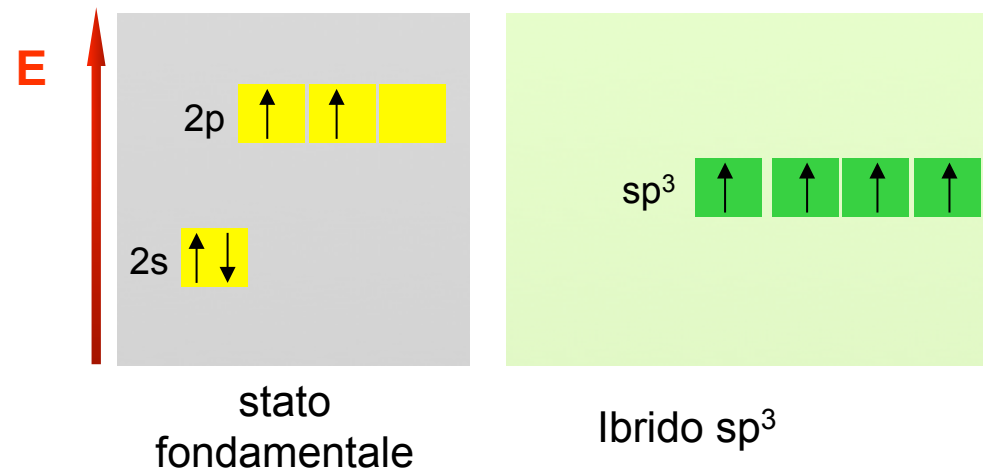
# Hybridization of orbitals in Carbon

For instance:  $\text{CH}_4$

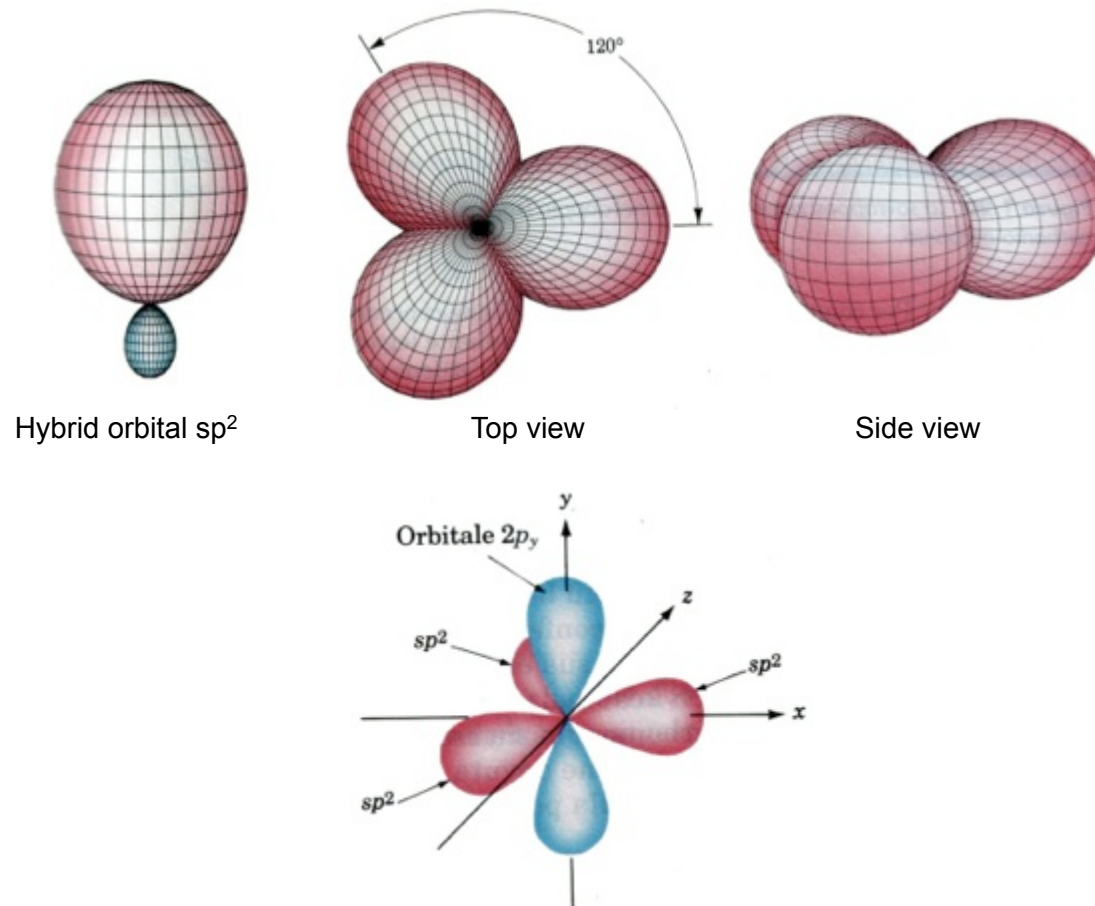
$[\text{He}]2s^2 2p^2$



$\text{AB}_4$ : tetraedrica

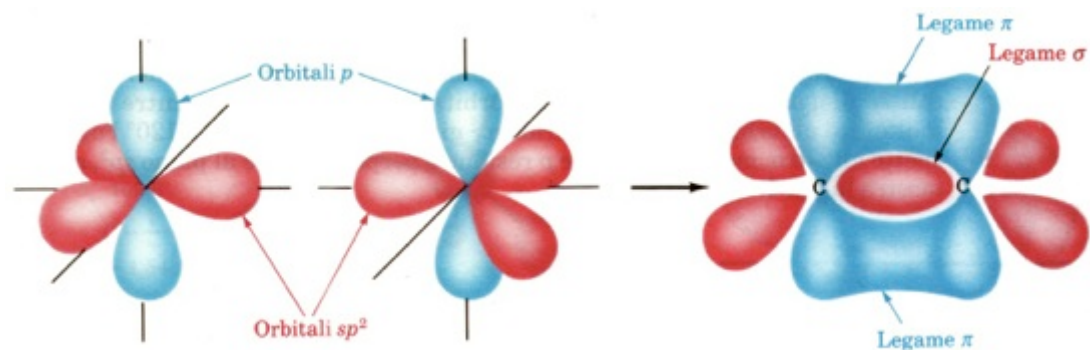


# Hybridization of orbitals in Carbon



*fig.1.1: un atomo di carbonio ibridizzato  $sp^2$  [3].*

# Carbon-Carbon bonding

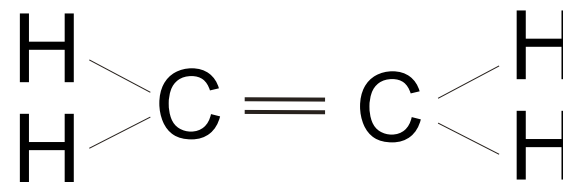
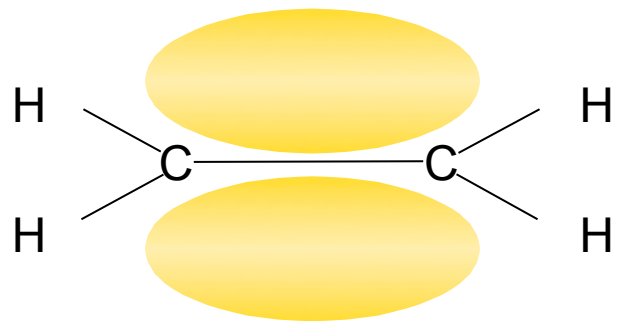
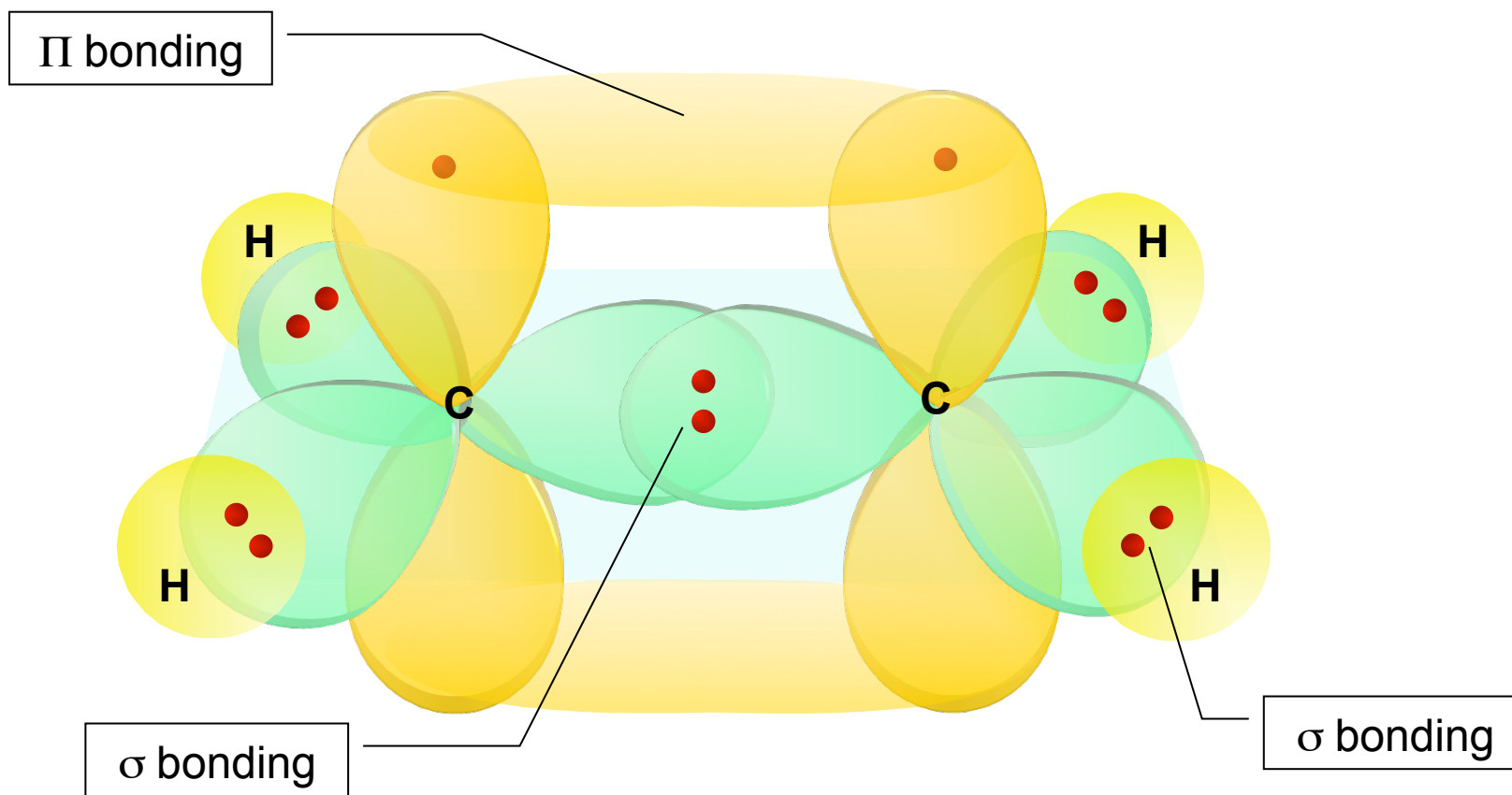


*fig.1.2: la sovrapposizione orbitalica nel doppio legame carbonio-carbonio [3].*

Molecular Orbital= linear combination of atomic orbitals (LCAO)

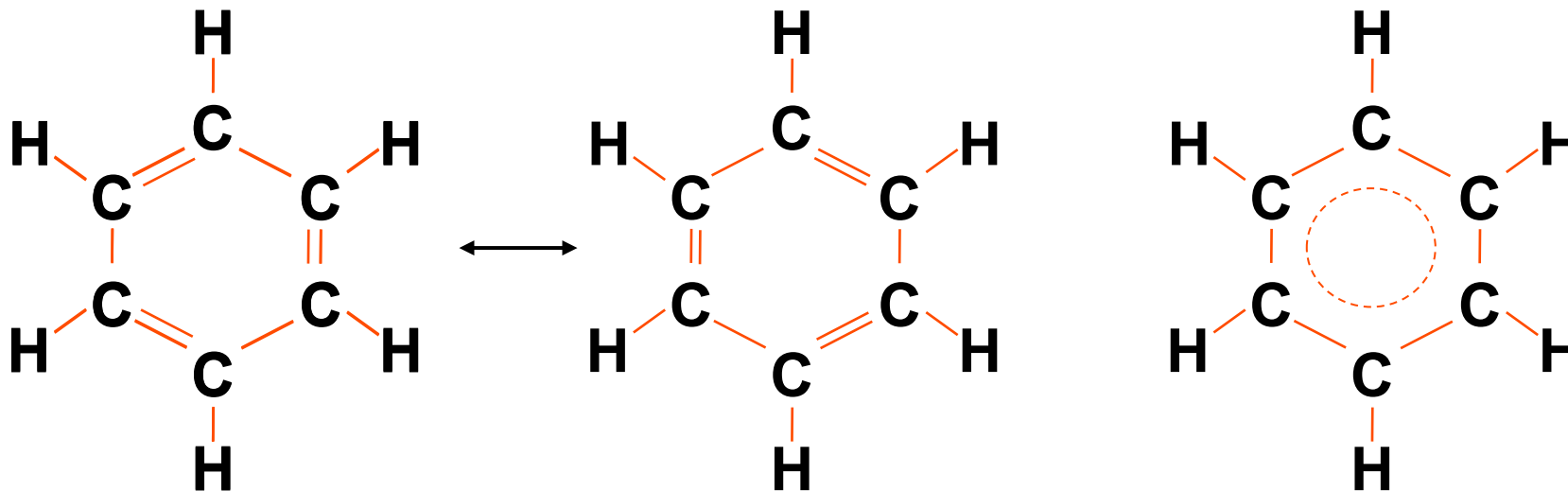


# Carbon-Carbon bonding



# Coniugated molecules

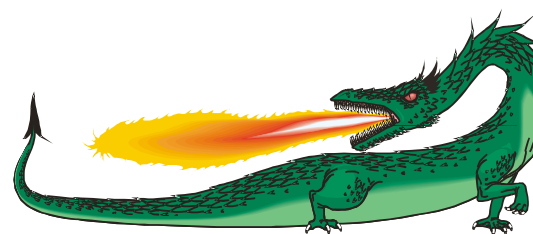
$C_6H_6$



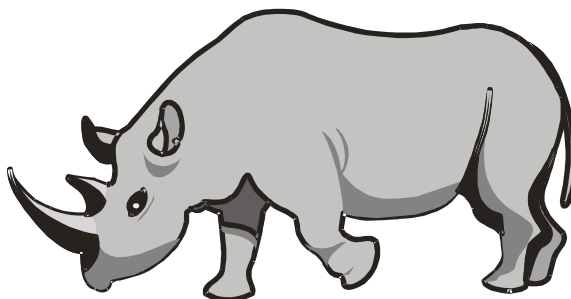
Limit formula



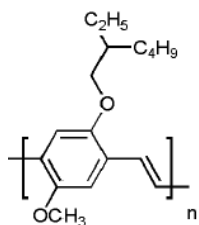
Limit formula



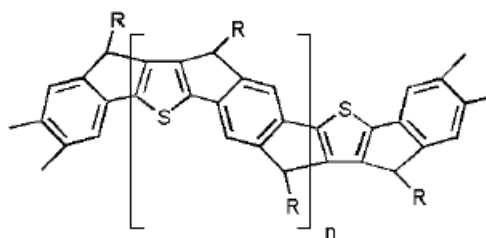
Real molecule



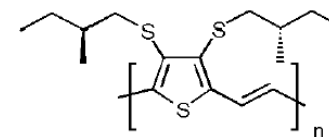
# Coniugated molecules



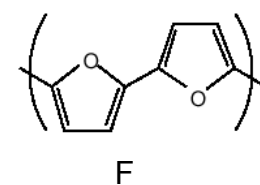
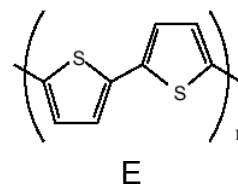
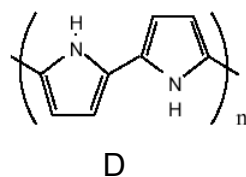
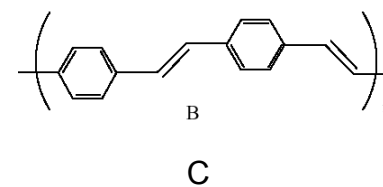
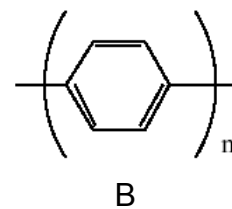
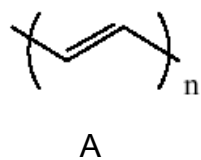
MEH-PPV



LPPPT

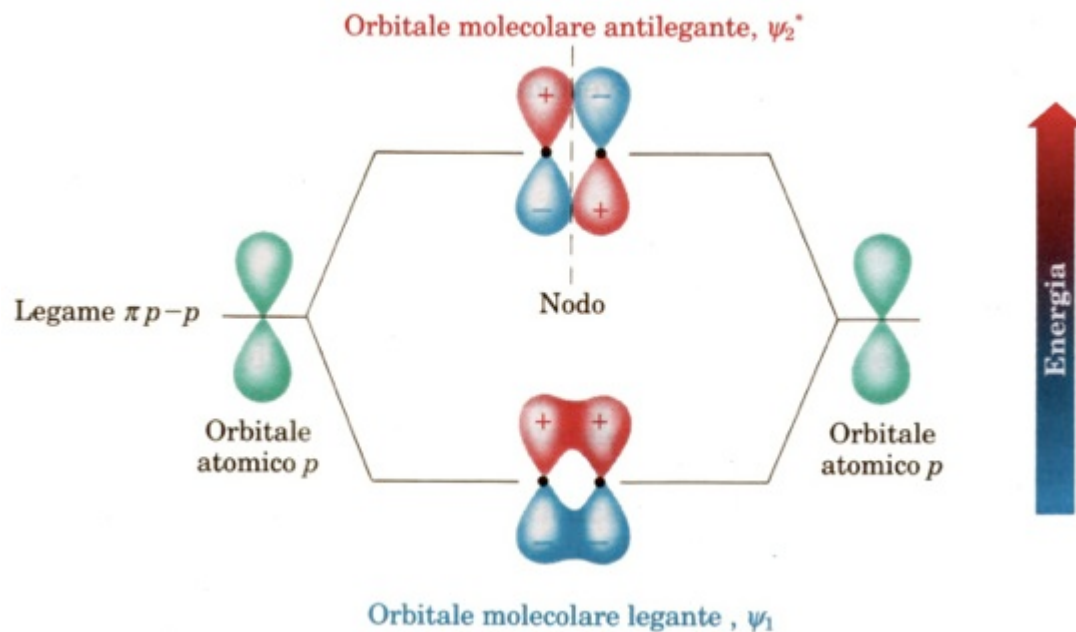


PTV



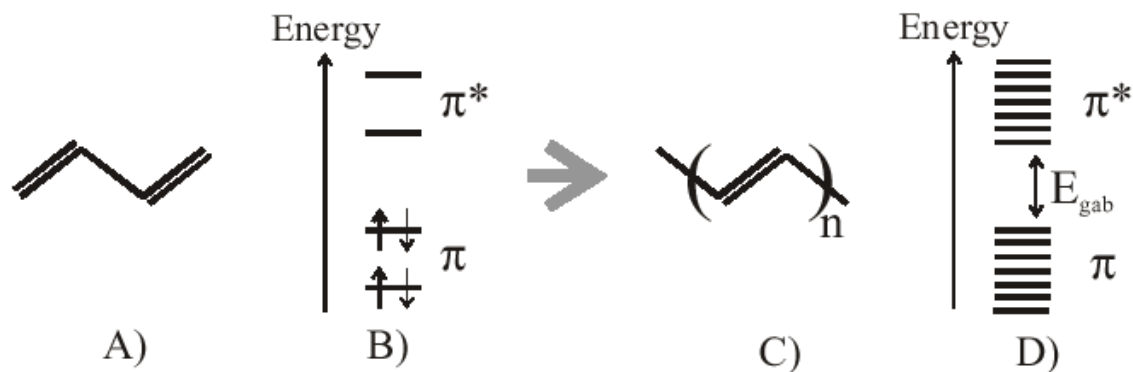
**fig.1.6: struttura molecolare di: A) trans-poliacetilene (PA); B) poli-para-fenilene (PPP); C) poli-fenile-vinilene (PPV); D) poli-pirrolo (PPy); E) poli-tiofene (PT); F) poli-furano (PF) [4].**

# Band Gap



Legame	Energia di legame (kJ · mol <sup>-1</sup> )
C—C	350
C—H	410
C—O	350
C—S	260
C—F	440
C—Cl	330
C—Br	280
C—I	240

fig.1.7: orbitali molecolari  $\pi$  leganti e antileganti [3].



Legame	Energia di legame (kJ · mol <sup>-1</sup> )
Si—Si	180
Si—H	300
Si—O	370
Si—S	230
Si—F	540
Si—Cl	360
Si—Br	290
Si—I	210



# Band Gap

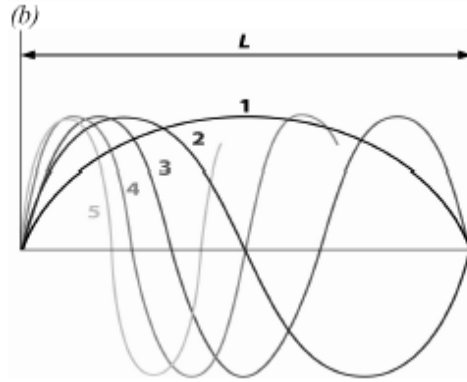


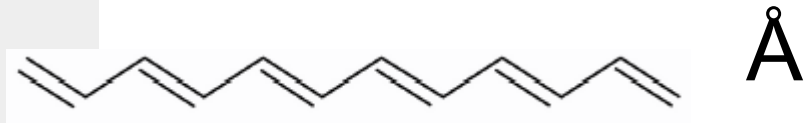
fig.1.10: funzioni d'onda dell'elettrone  $\pi$  nella buca di potenziale profonda infinito [6].

$L$  = coniugation length = length of the shortest molecular segment with a perfect alternation of single and double bonds;  $N$  = number of atoms (each with 2 electrons);  $d$  = atomic distance

$$E_n = \frac{n^2 h^2}{8mL^2} \longrightarrow \begin{array}{l} E(\text{HOMO}) = \frac{\left(\frac{N}{2}\right)^2 h^2}{8m(Nd)^2} \\ E(\text{LUMO}) = \frac{\left(\frac{N}{2} + 1\right)^2 h^2}{8m(Nd)^2} \end{array} \longrightarrow E_G = E(\text{LUMO}) - E(\text{HOMO}) = \frac{(N+1)^2 h^2}{8m(Nd)^2} \approx \frac{h^2}{8md^2 N}$$

The highest  $N$ , the lowest the gap

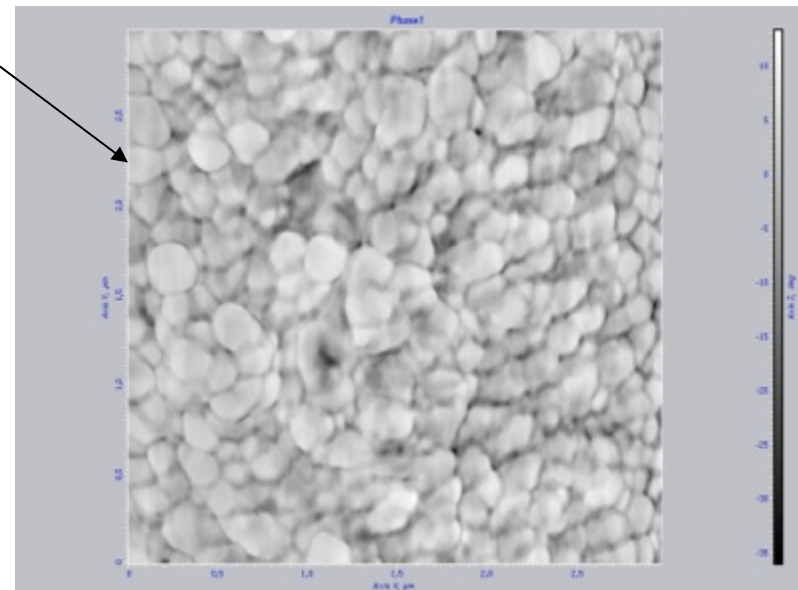
# Charge transport in organic semiconductors



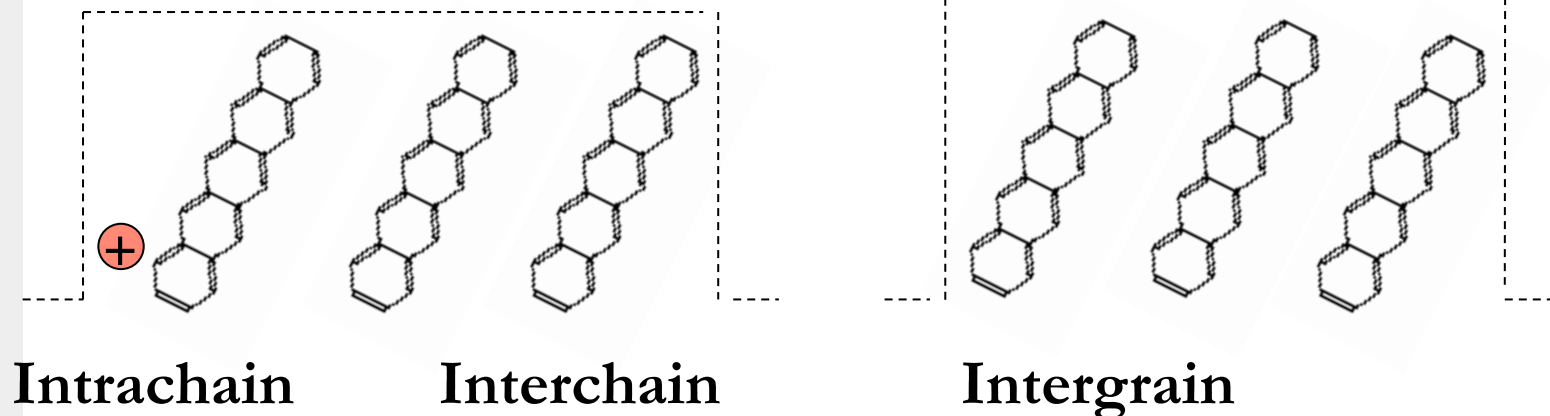
nm



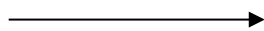
μm



# Charge transport in organic semiconductors

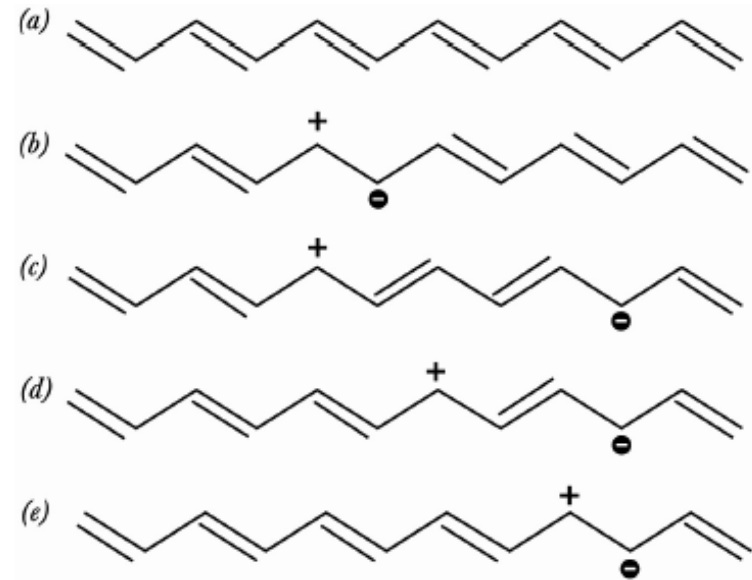
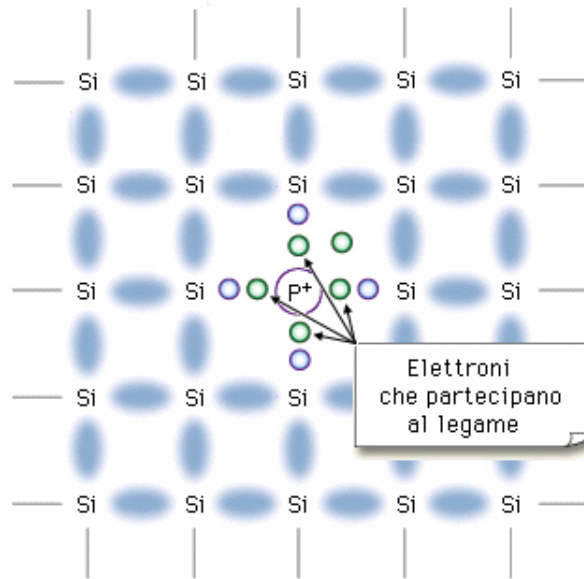


3 coesistent mechanisms+ charge injection from contacts



Measurements difficult to explain

# Doping and charge transport



In inorganic semiconductor, doping is substitutional and causes an increase in free charge carrier concentration. These carriers move in a periodic potential with no interaction with the crystal (*band model*).

In organic, doping is not substitutional: supplementary charge physically interact with molecules causing a perturbation in the conjugated chain. This perturbation (charge + deformation induced by the charge) is called **polaron**

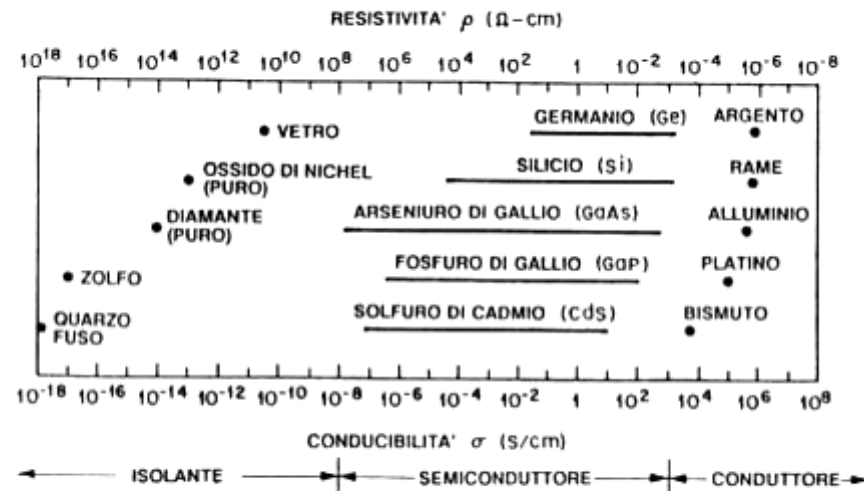


# Doping and charge transport

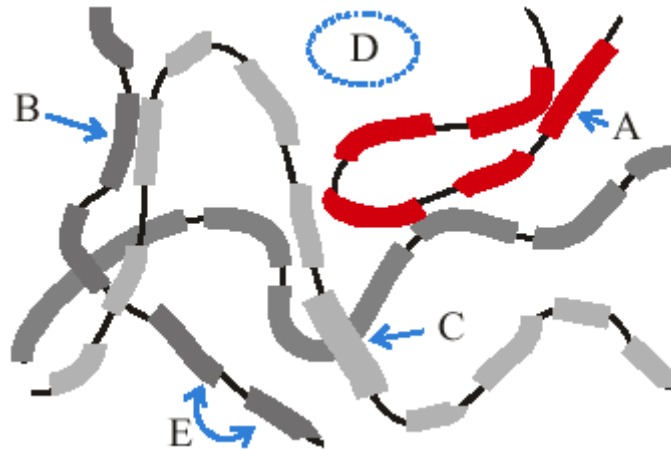
In analogy with inorganic semiconductors, the polaron can be roughly described as a charge free of moving along the chain strongly interacting with the semiconductor lattice

**$m_{\text{eff}}(\text{polaron}) \gg m_{\text{eff}}(\text{free charge carrier})$**

**$\rightarrow \text{mobility}(\text{polaron}) \ll \text{mobility}(\text{free charge carrier})$**



## Intermolecular transport: hopping

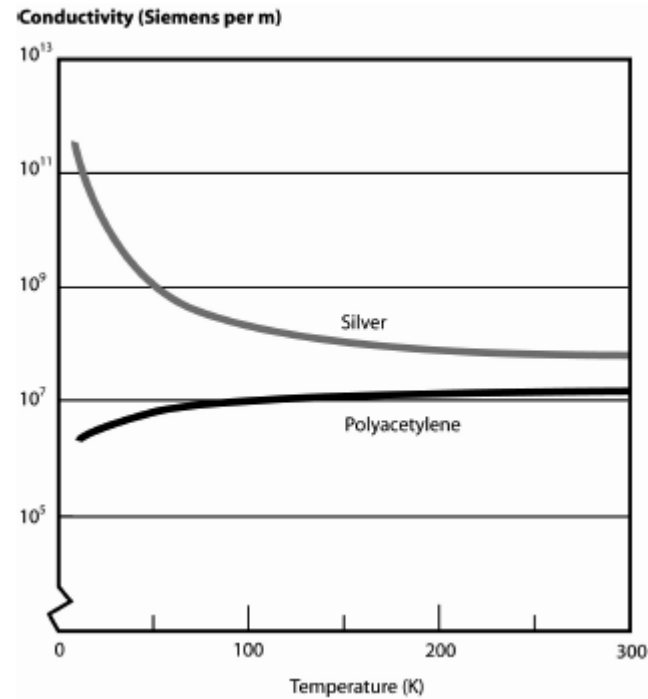


hopping = tunneling between crossing chains

To move, the charge carrier needs energy that can be provided by phonons (increasing with temperature)

$$\mu_D = \frac{e \cdot d^2}{2\tau_J \cdot k_B \cdot T} \quad \longrightarrow \quad \sigma(T) = \sigma_0(T) \cdot \exp[-(T_0/T)^{1/(1+d)}]$$

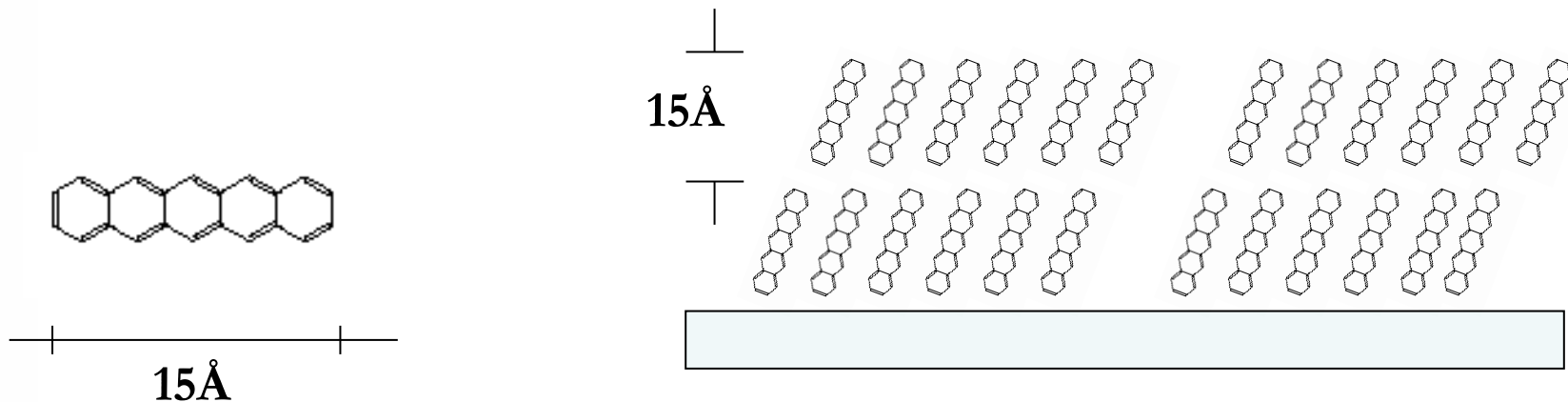
# Intermolecular transport: hopping



But, in organic materials there is a great variety of behaviour from material to material. A unifying theory has not yet been developed.

## Intergrain transport: Pentacene ( $C_{22}H_{14}$ )

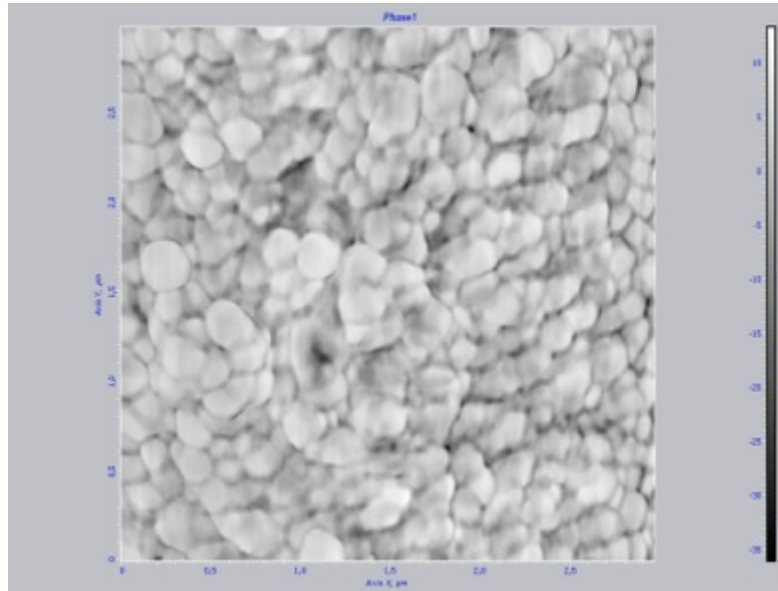
- 5 benzene rings
- Non soluble. Deposited by evaporation
- Molecules stand perpendicular to the substrate.
- Molecules form separated domains (grains)



Materials for “Plastic Electronics”



# Intergrain transport: Pentacene ( $C_{22}H_{14}$ )



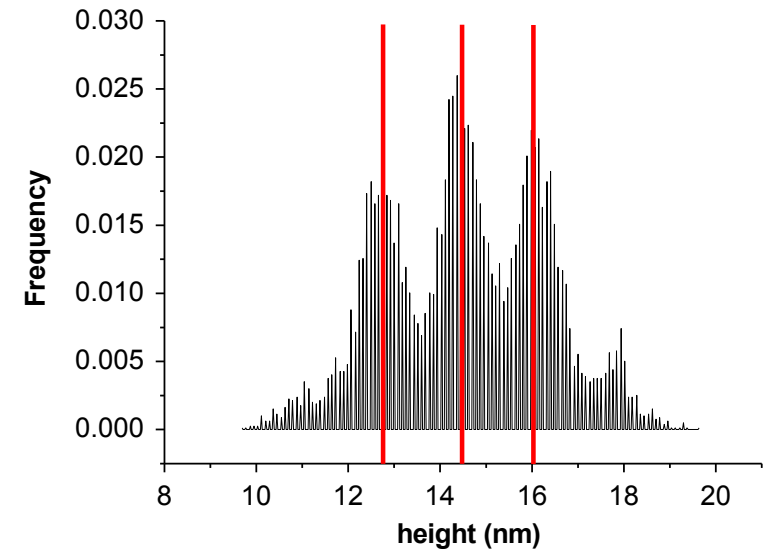
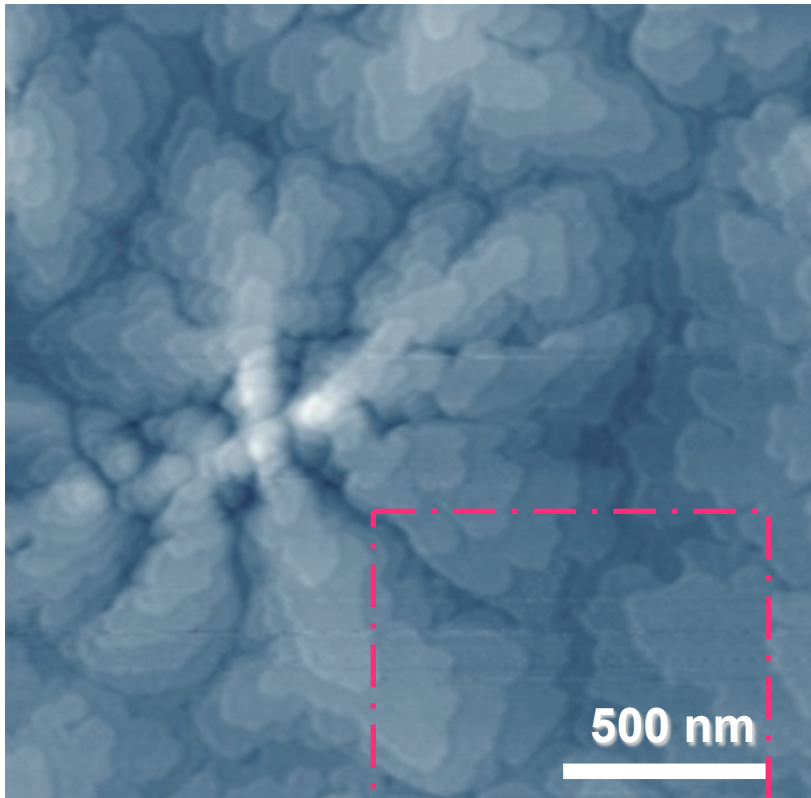
## Conduction:

- hopping
- thermally activated
- limited by traps at grain boundaries

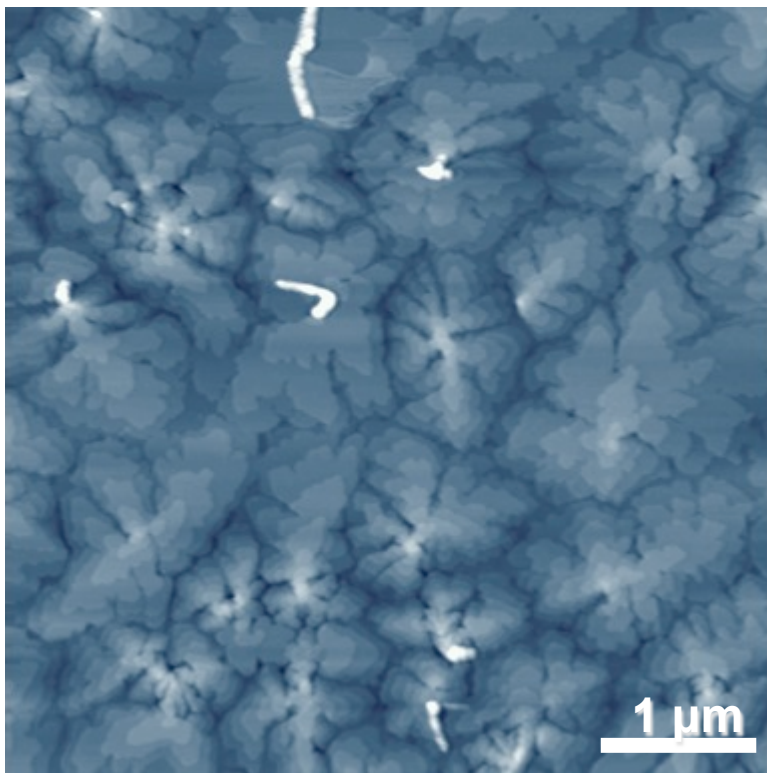
$$\frac{1}{\mu} = \frac{1}{\mu_{\text{bulk}}} + \frac{1}{\mu_{\text{traps}}}$$

Correlation btw grain dimensions and mobility

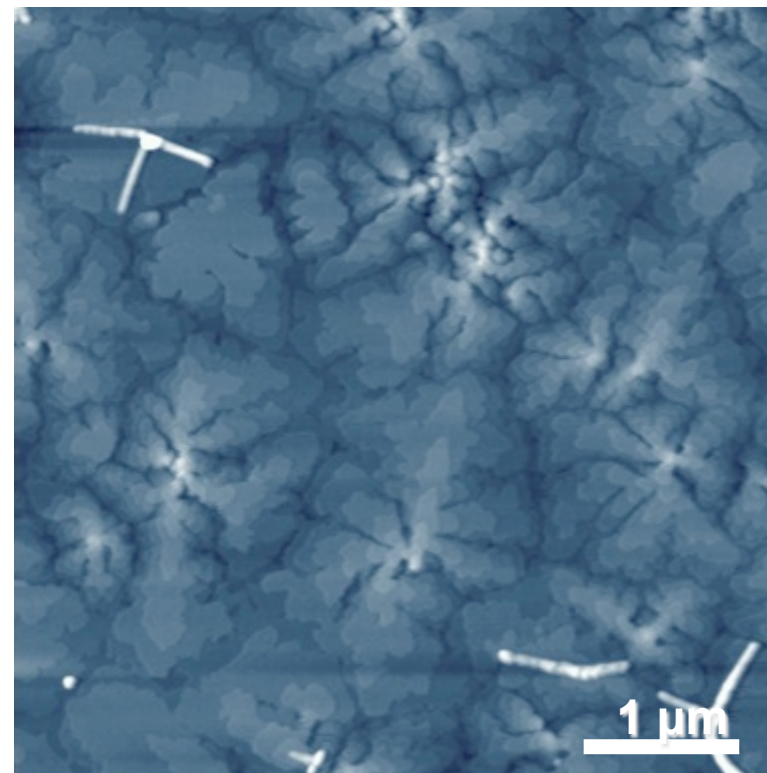
# Influence of surface morphology



## Influence of surface morphology

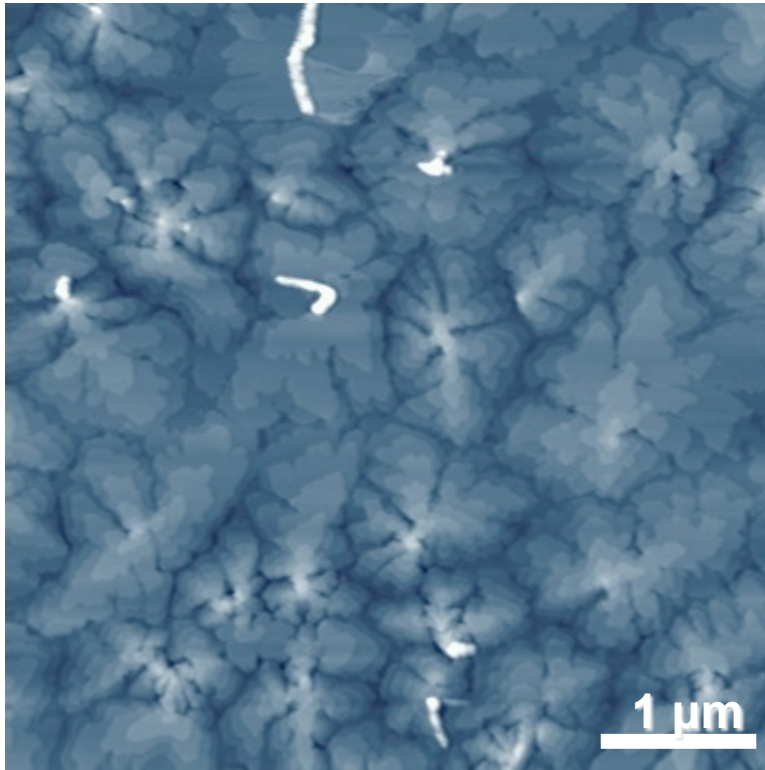


**Pentacene on Mica**

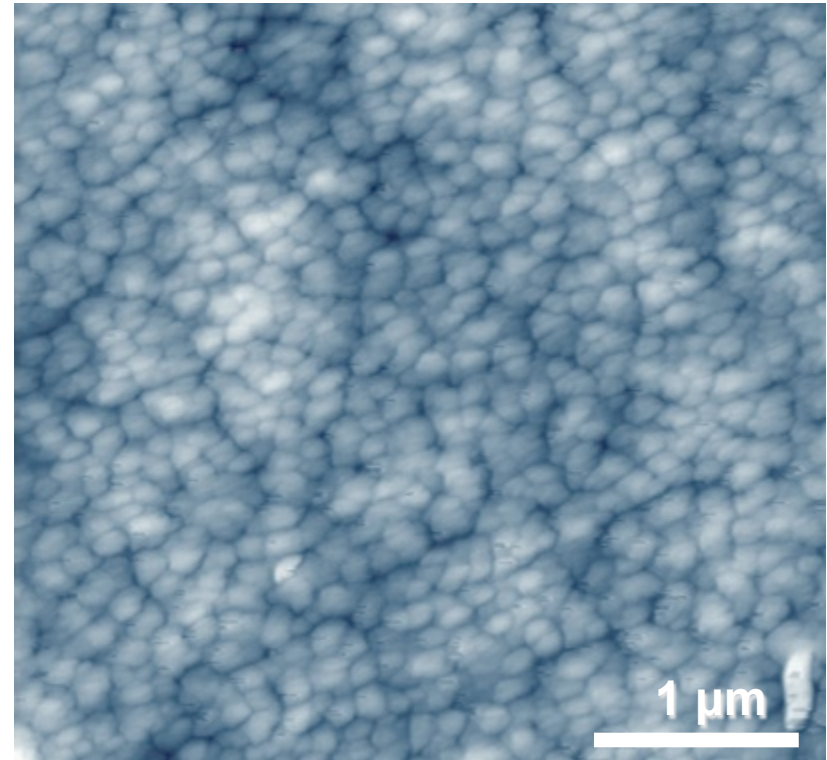


**Pentacene on SiO<sub>2</sub>**

## Influence of surface morphology



**Pentacene on SiO<sub>2</sub>**



**Pentacene on Mylar**

# Outline seconda parte

**Organic Thin Film Transistors (OTFTs)**

**Contatti metallo-semiconduttore organico**

**Comportamento elettrico degli OTFT**

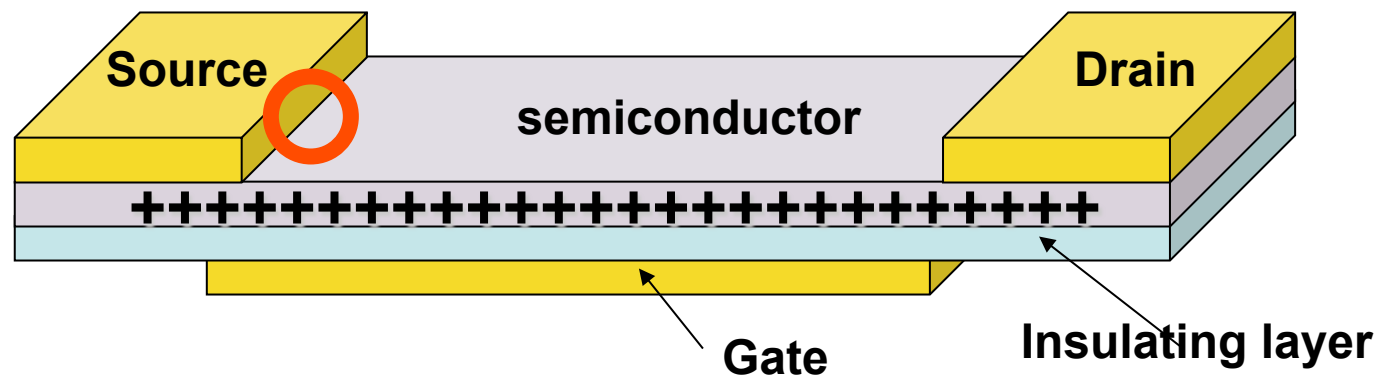
**Modello elettrico del dispositivo**

**Tecnologia**

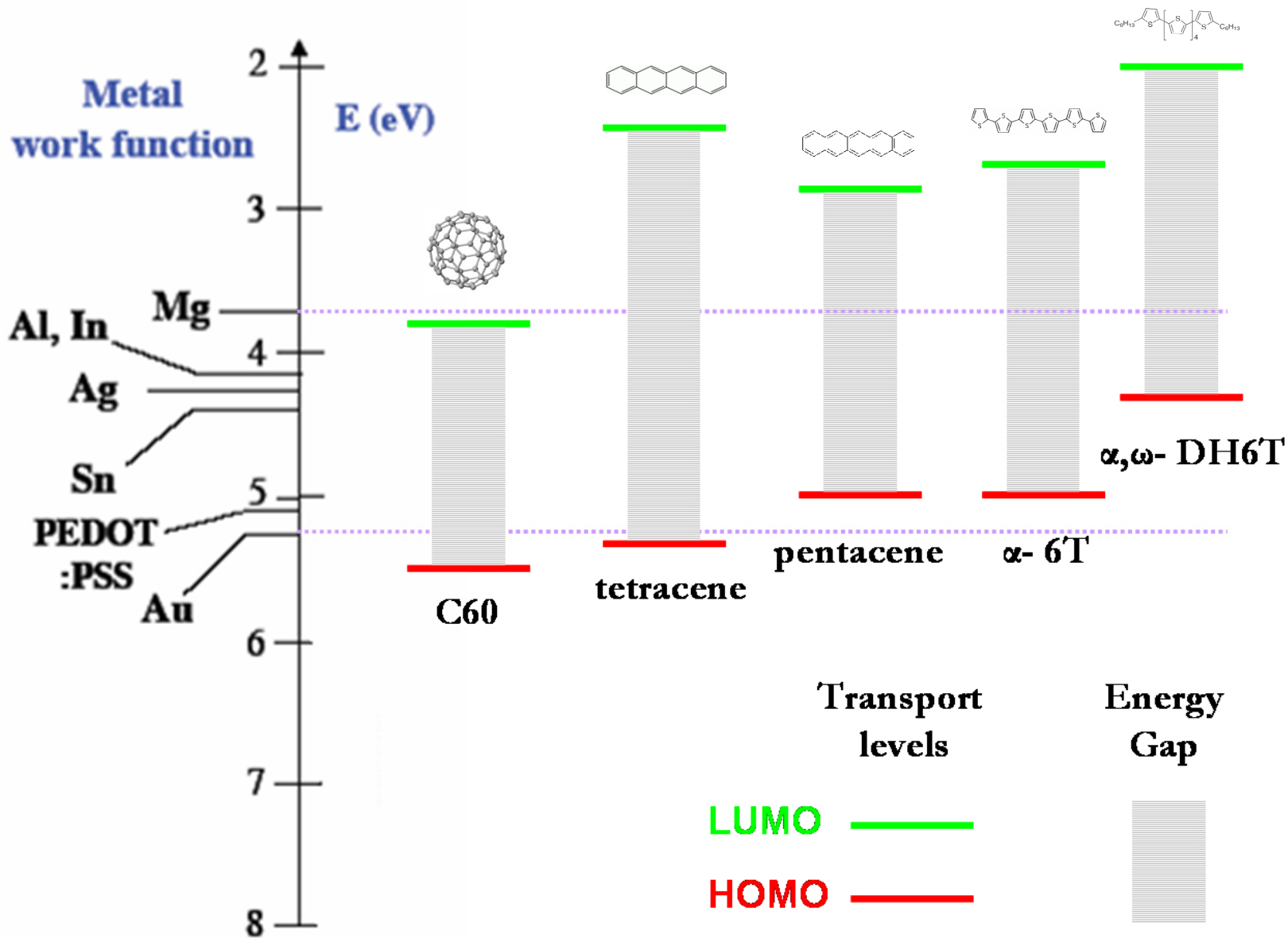
# Field Effect Transistors

OTFT = ORGANIC THIN FILM TRANSISTOR

Interface metal - semiconductor



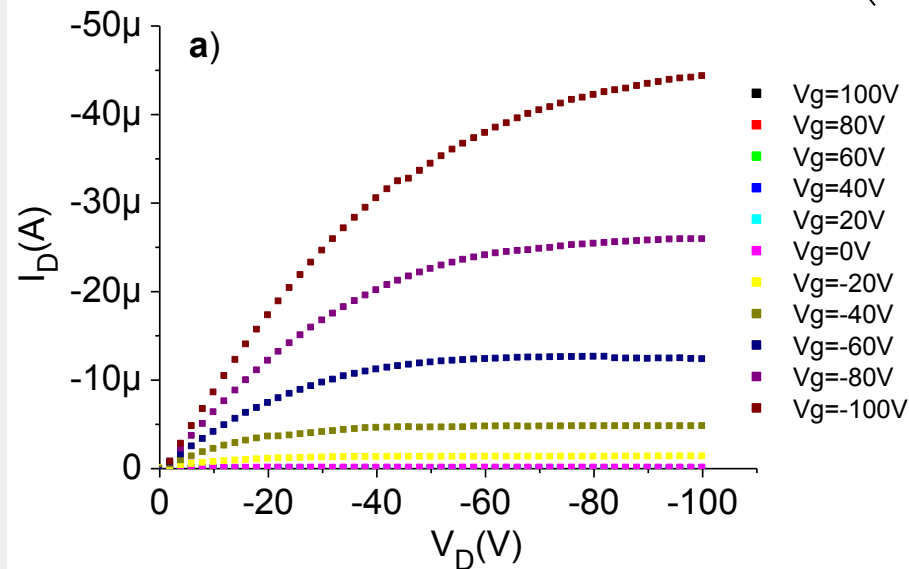
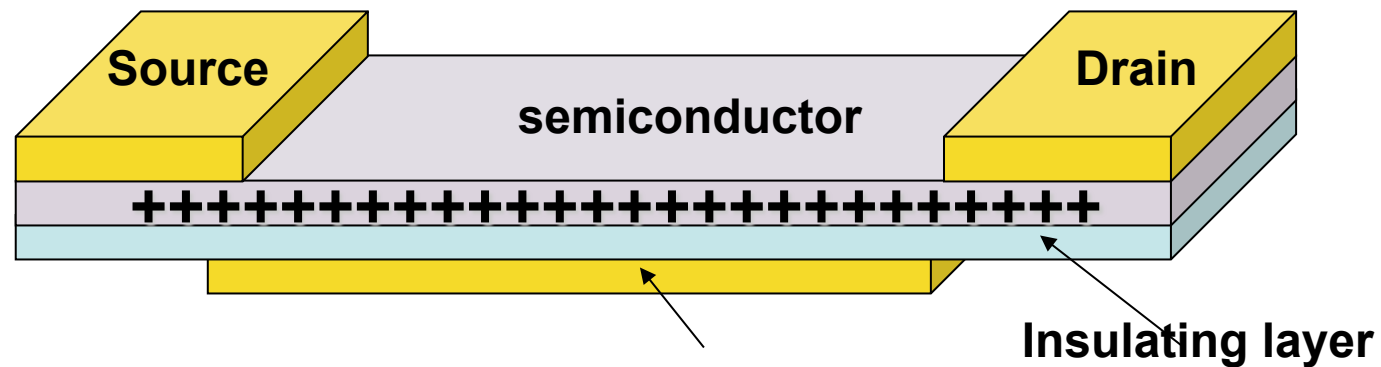
# Charge injection from metal contacts





# Thin Film Transistor

TFT model was first developed for poorly conductive semiconductors like amorphous Si



Typically p-type!



# How an OTFT works

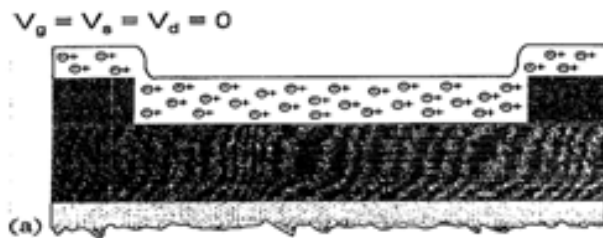


Fig. 2a

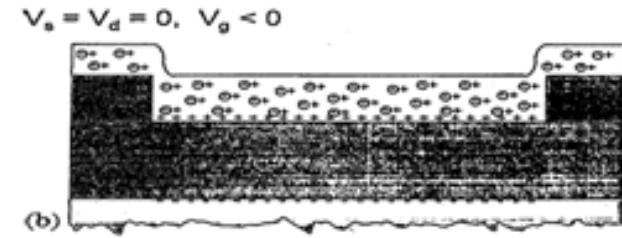


Fig. 2b

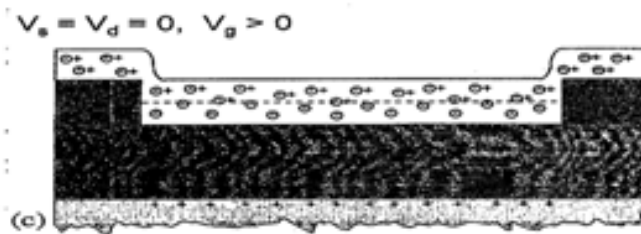


Fig. 2c

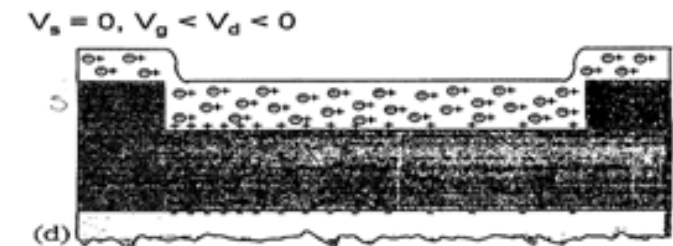


Fig. 2d

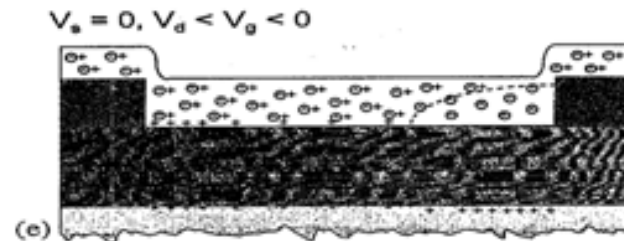
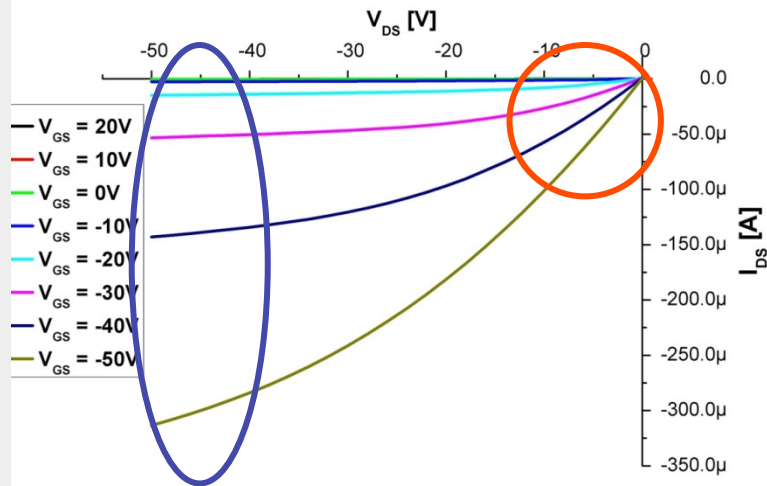


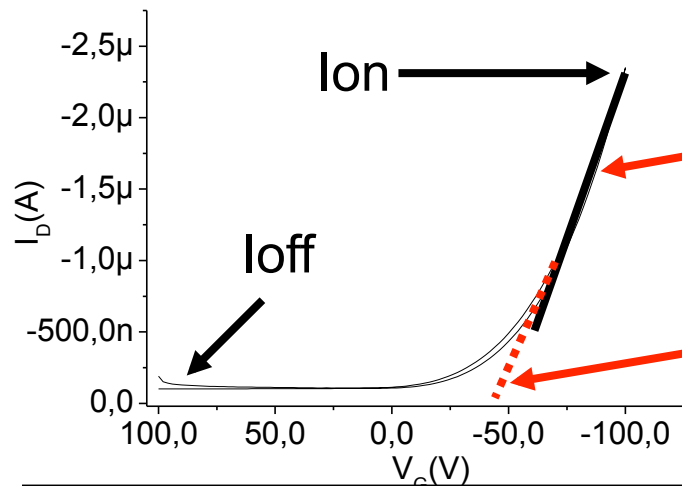
Fig. 2e

# Equations and extraction of parameters



Linear region:  $I_D = \mu C_{ox} \frac{Z}{L} (V_G - V_T) V_D$

Saturation region:  $I_D = \frac{1}{2} \mu C_{ox} \frac{Z}{L} (V_G - V_T)^2$



$$\left. \frac{\partial I_D}{\partial V_G} \right|_{sat} = \mu C_{ox} \frac{Z}{L} (V_G - V_T)$$

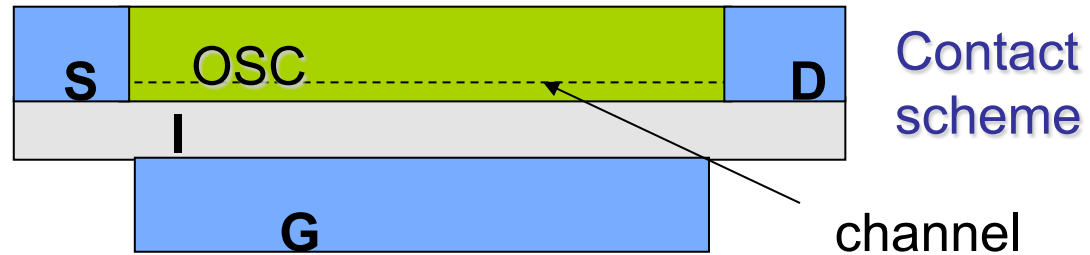
Important parameters:

$$\frac{I_{on}}{I_{off}}, \mu, V_T$$

Typical values:

$$\begin{aligned} \mu &\sim 10^{-2}: 10^{-1} \\ I_{on}/I_{off} &\sim 10^4 : 10^5 \\ V_T &\sim -10: +10 \text{ V} \end{aligned}$$

# Structures and fabrication techniques

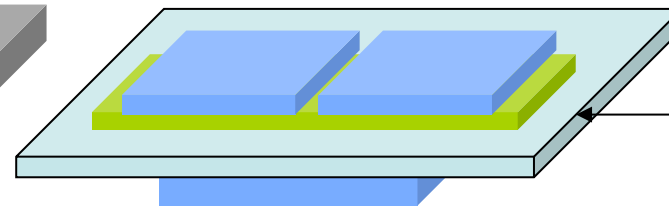
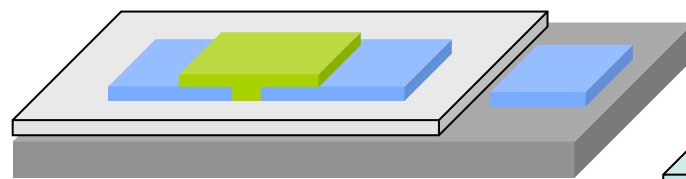
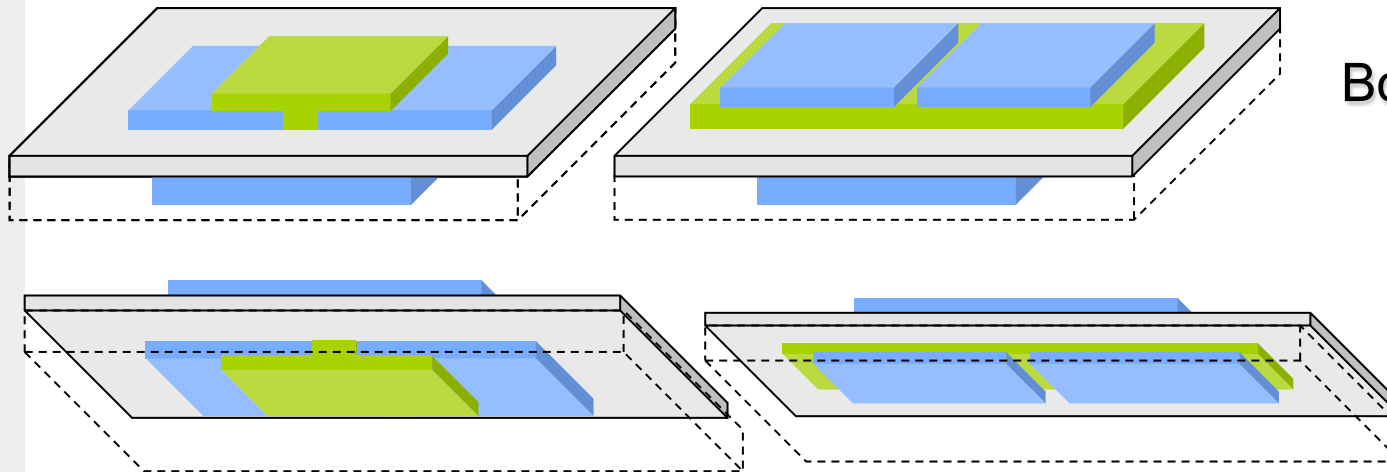


Bottom contact

Top contact

Bottom gate

Top gate



Si/SiO<sub>2</sub> substrate

Substrate-free

Free-standing insulating layer

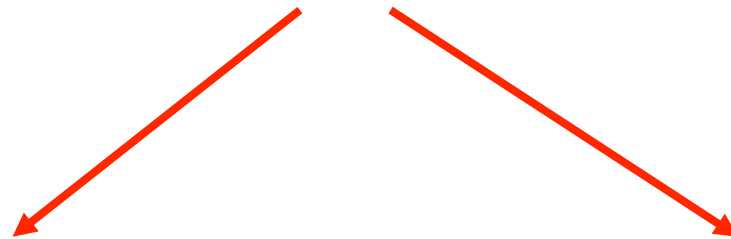
# Materials and fabrication techniques

Materials:

Electrodes: metals, conductive polymers

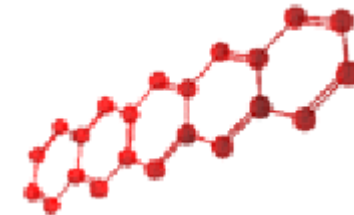
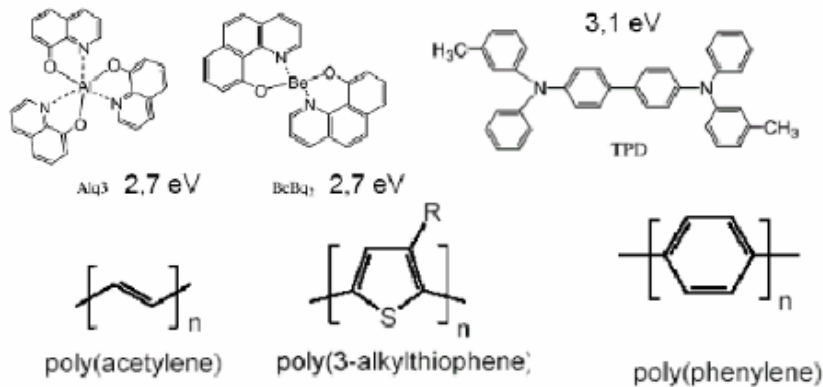
Insulating layers: polyimide, PVA, PVP,...

Organic semiconductors



Solution processable  
Polymers

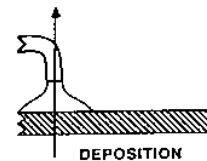
Small molecules  
(deposited by  
evaporation)



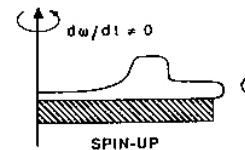
# Fabrication techniques - Spin Coating

Low cost technique for liquid phase materials

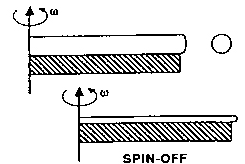
Deposition



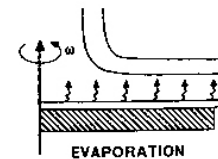
Spin up



Spin off



Spin down



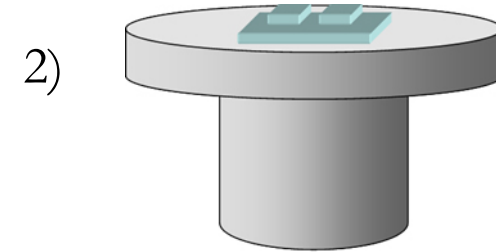
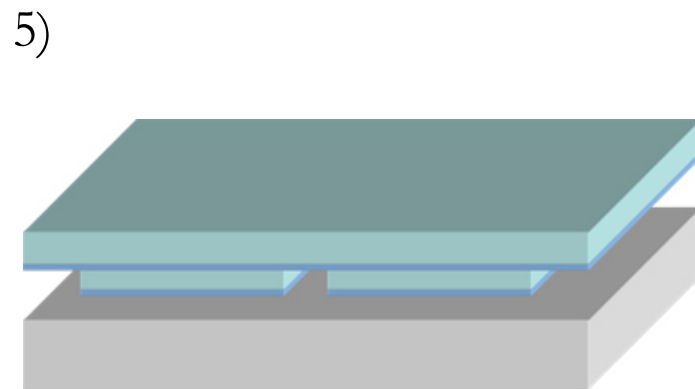
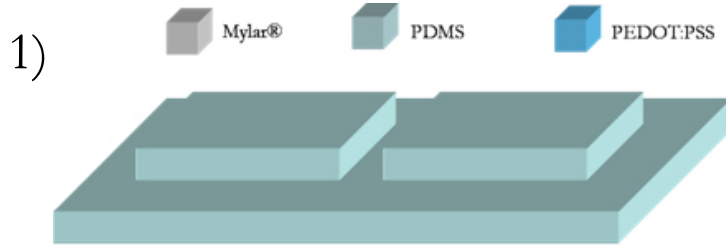
Thermal annealing (dewetting)

Process parameters:

1. Spin up time
2. Spin speed
3. Spin off time
4. Spin down time
5. Dewetting time
6. Dewetting T

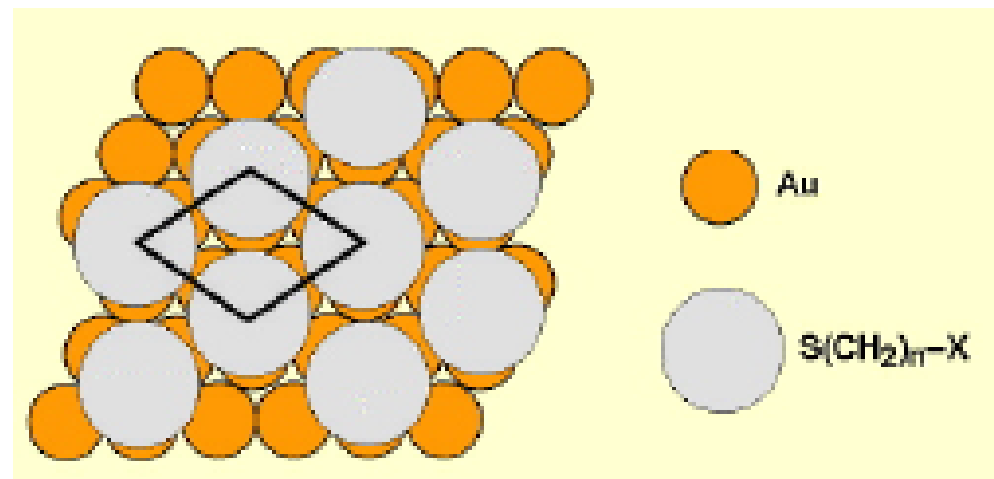
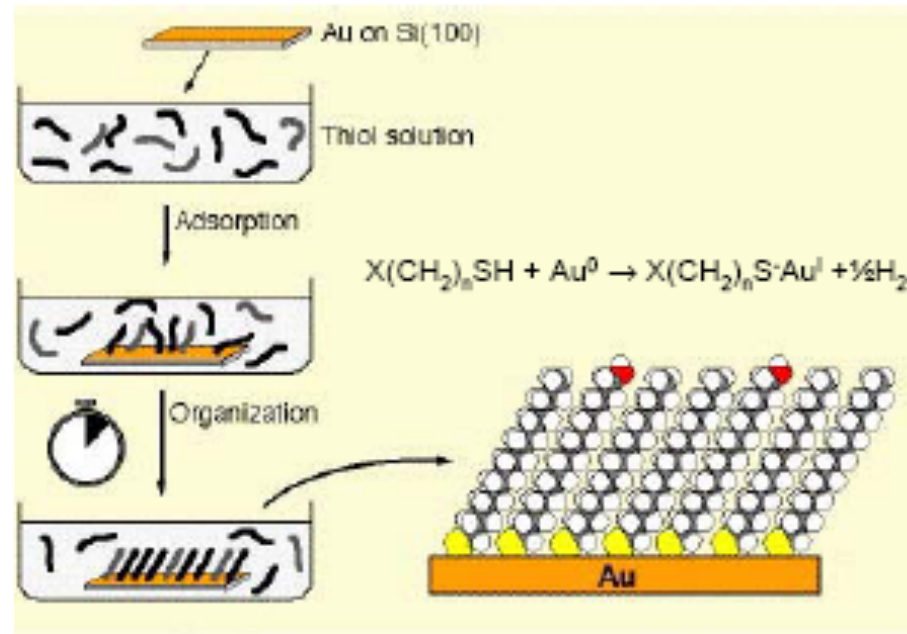
**Adv: simple and low cost**

# Fabrication technique – Soft Lithography



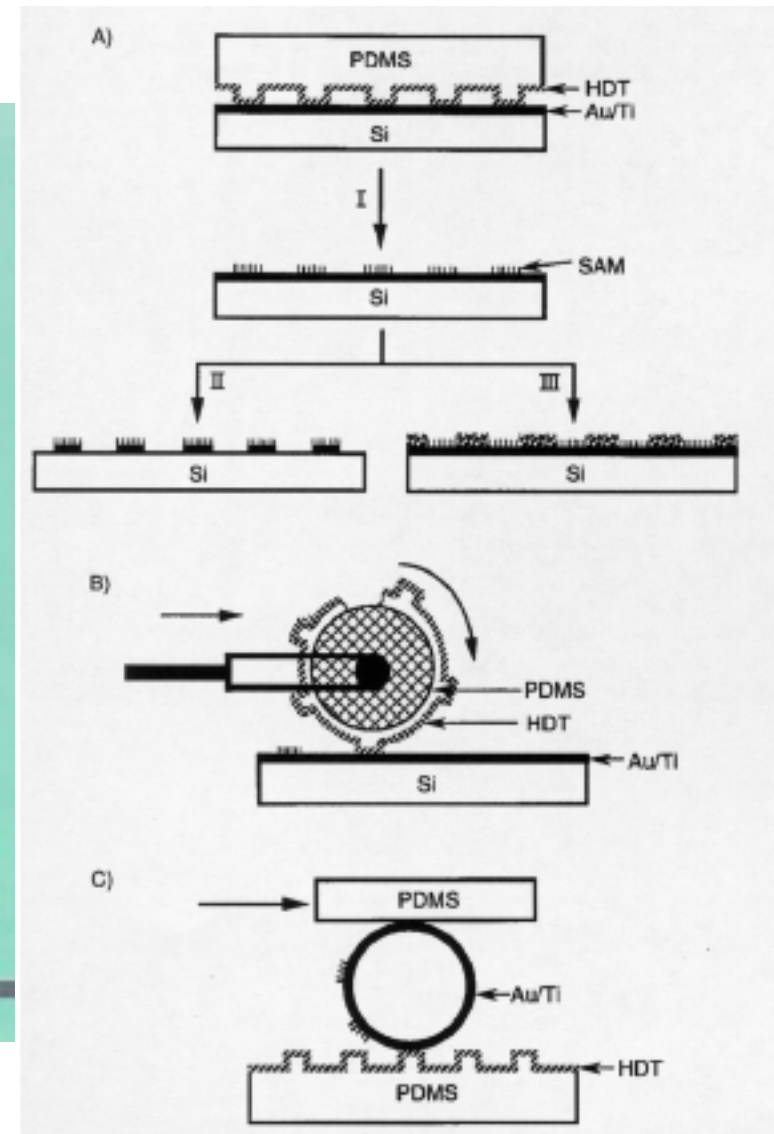
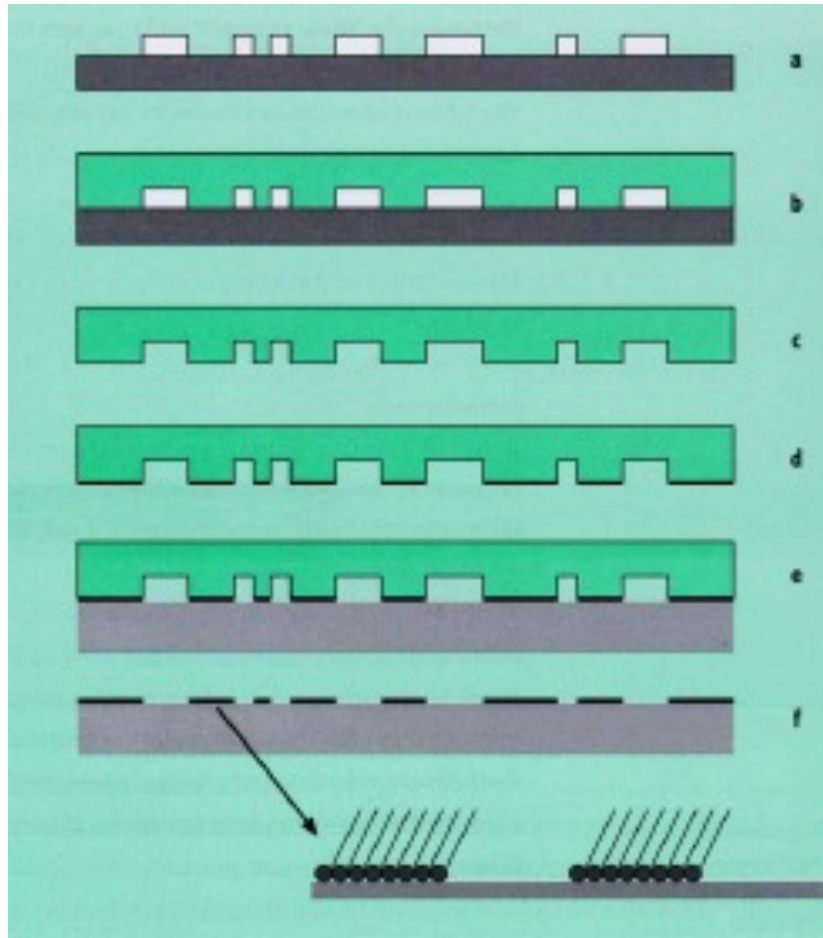
# Fabrication technique – Soft Lithography

## Inks instead of resist for patterning metals



# Fabrication technique – Soft Lithography

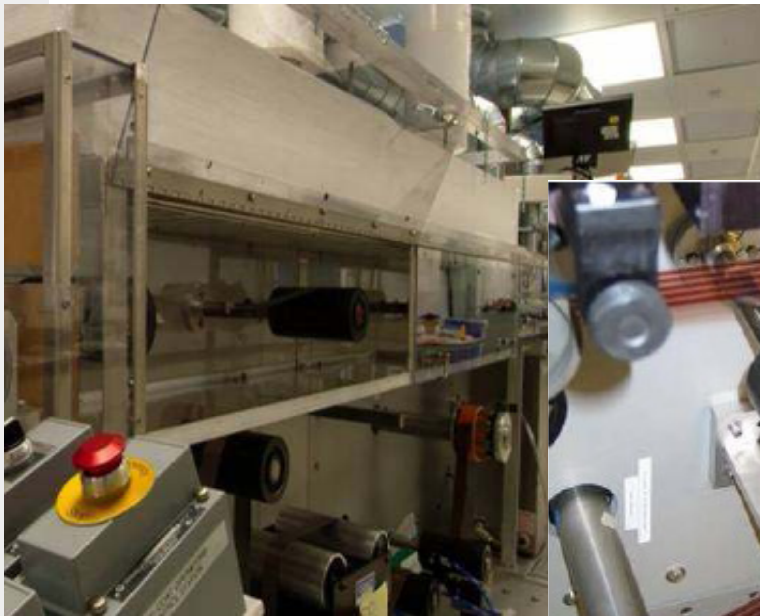
## MicroContact Printing





# Printing & Roll to Roll

## Printing



# Possible applications for OTFTs

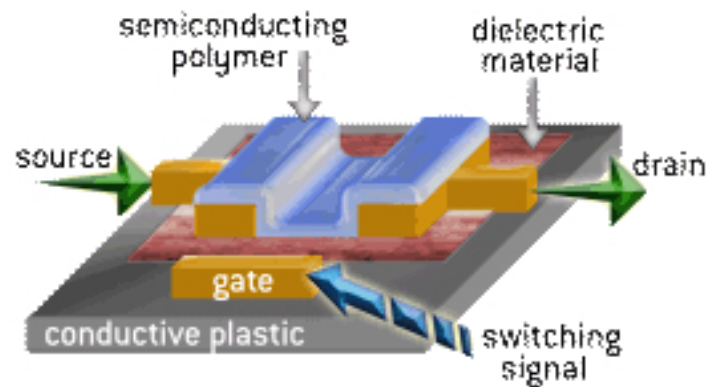
cheap dynamic signs



wearable electronics



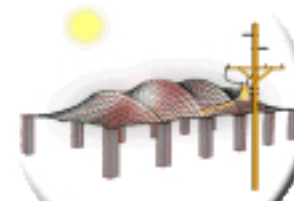
sensors



electronic paper



RFID tags



flexible solar cells

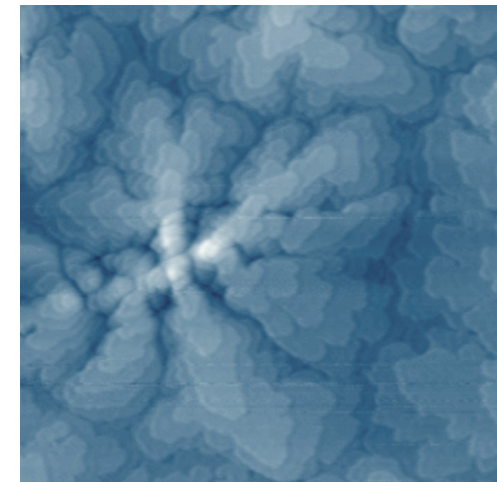
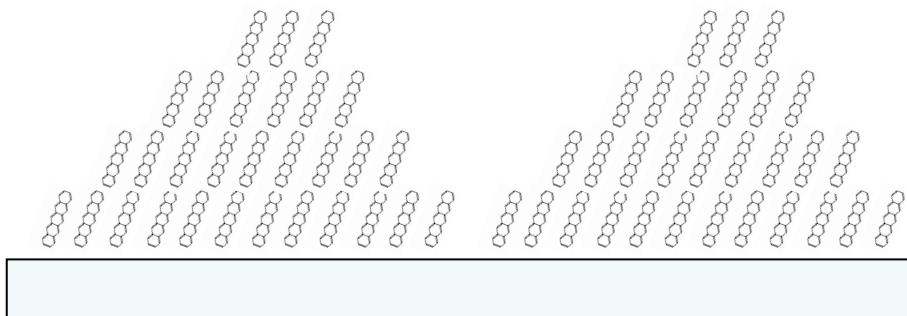
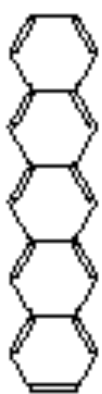
# Outline terza parte

**Sensori per variabili meccaniche**

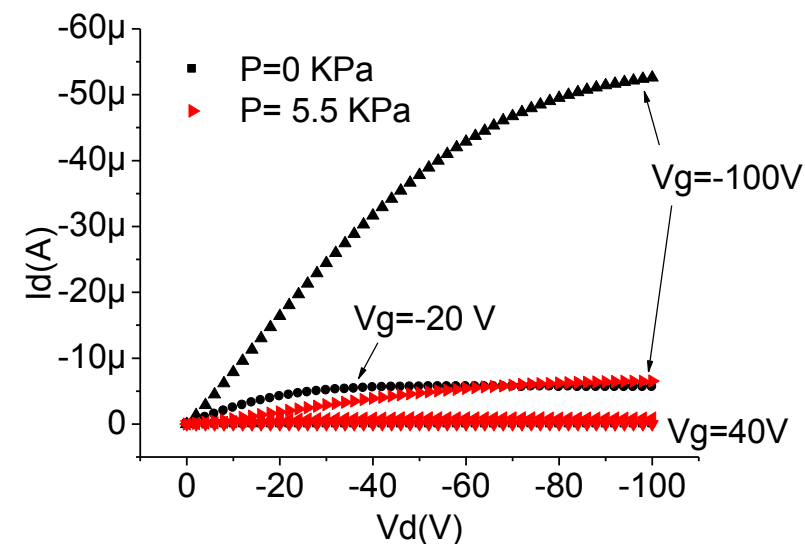
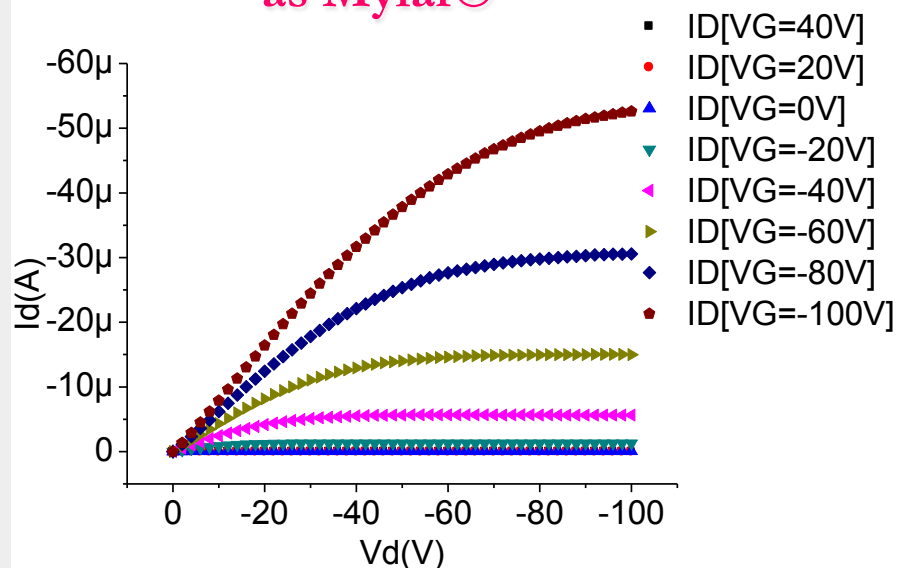
**Sensori per variabili chimiche: ISOFET**

**Prospettive applicative**

# OFET based mechanical sensors



Nice molecular ordering, even when deposited on “non ideal” substrate as Mylar®

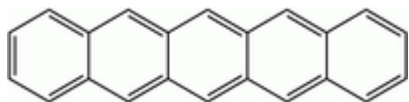


$I_D$  always decreases when mechanical stimulus is applied

I. Manunza et al., *Appl. Phys. Lett.* 89, 143502 (2006)

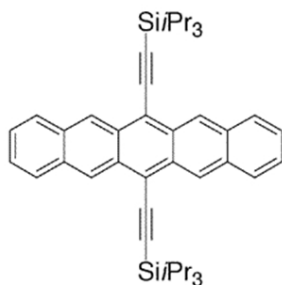
I. Manunza et al., *Bios. Bioelec.* 22, 2775, (2007)

## Different OS can be employed



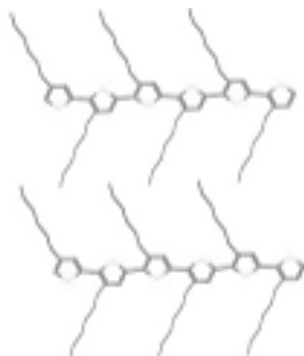
Pentacene

*Not soluble*



Tri-isopropylsilylethynyl  
(TIPS) Pentacene

*Soluble*

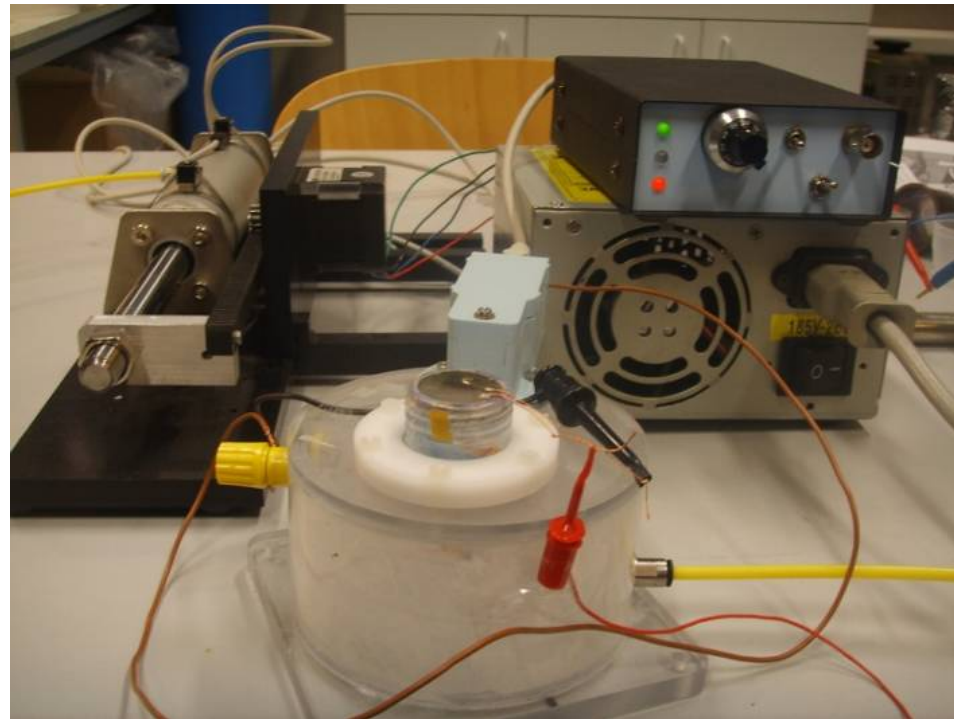
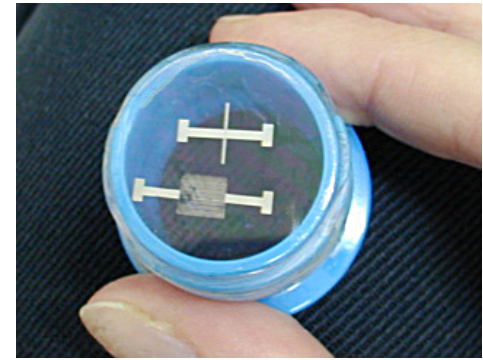
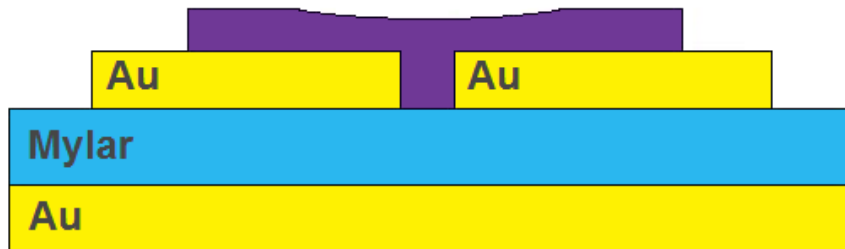


poly(3-hexylthiophene)  
(P3HT)

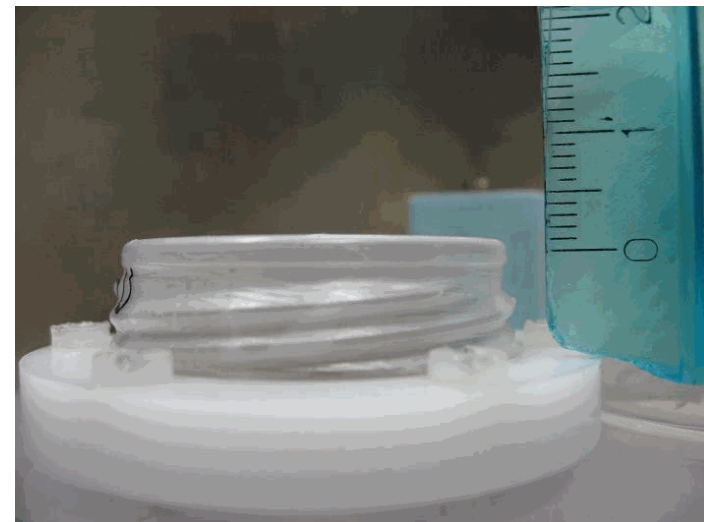
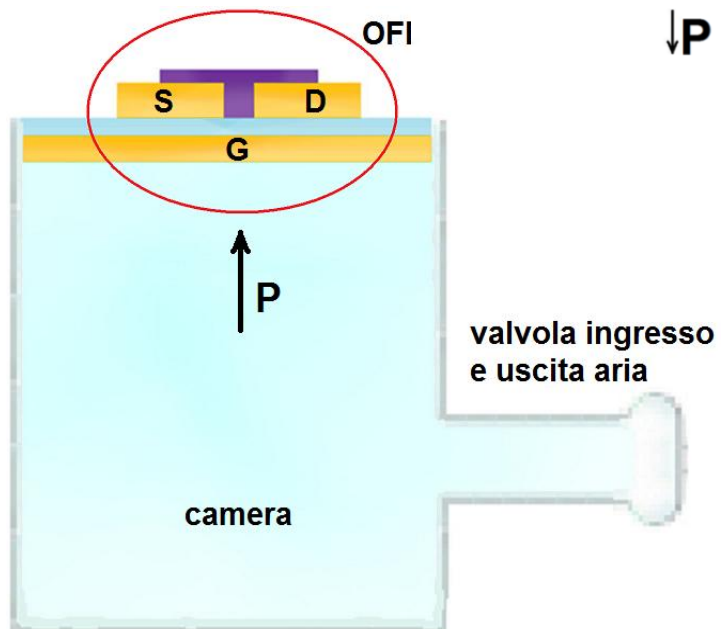
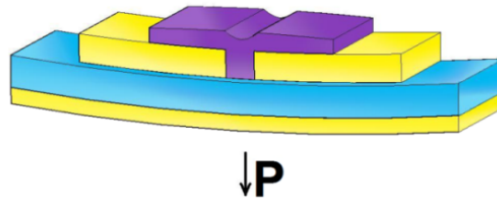
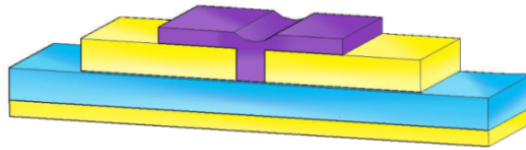
*Soluble*



# Pressure sensors: set up



# Pressure sensors: set up



# Pressure Sensors: pentacene

Current decreases when pressure is applied

both for positive and negative  $P$

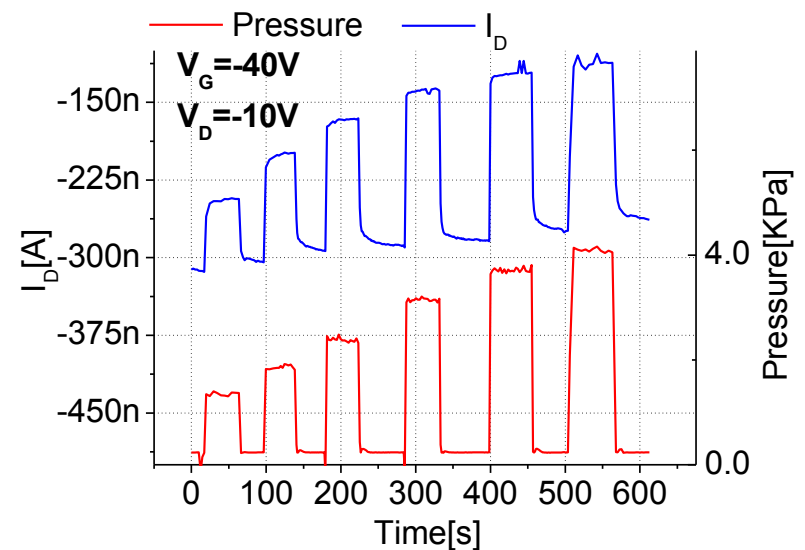
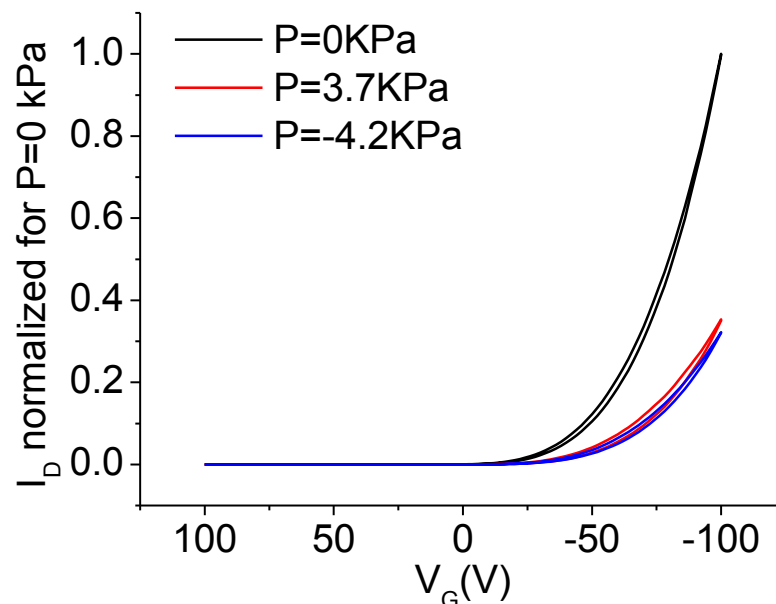
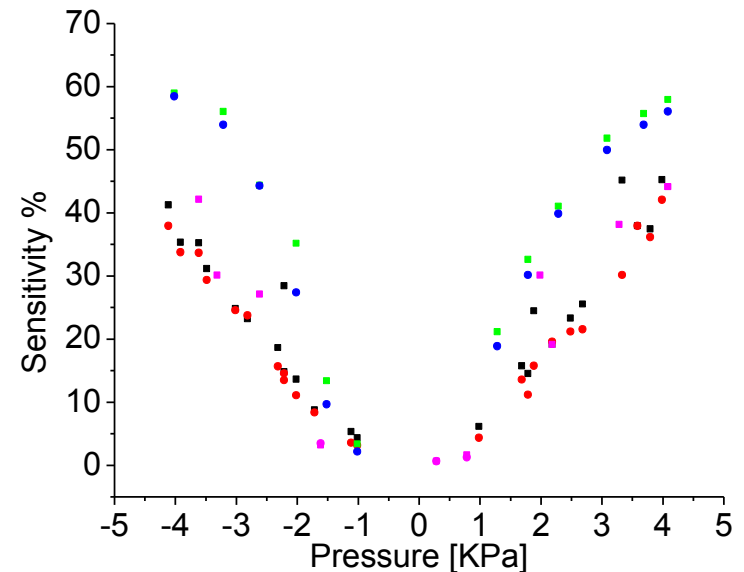
High sensitivity around 45 to 60%

Response, rise and fall time  $\approx 100\text{ms}$

Short TS  $\uparrow >$  around 5-10s

$\downarrow >$  around 5-10s

Hysteresis increases for  $P > 2.5\text{kPa}$





# Pressure Sensors: P3HT

Current decreases when pressure is applied **both for positive and negative P**

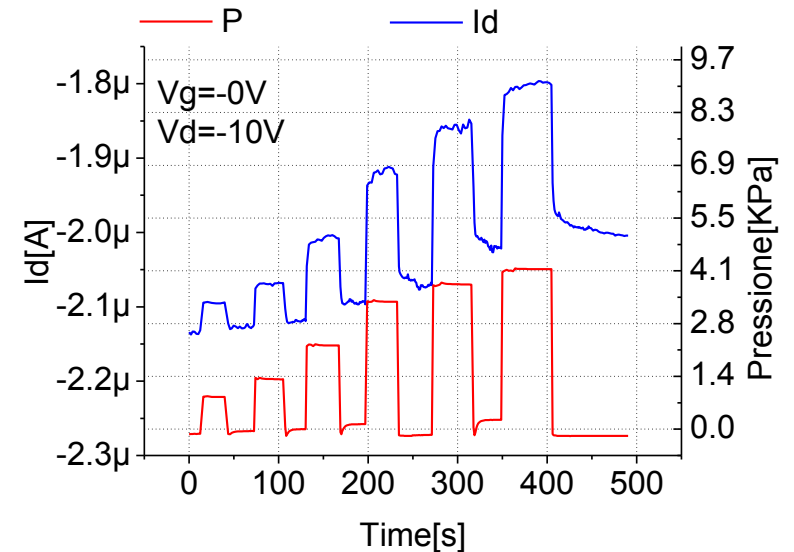
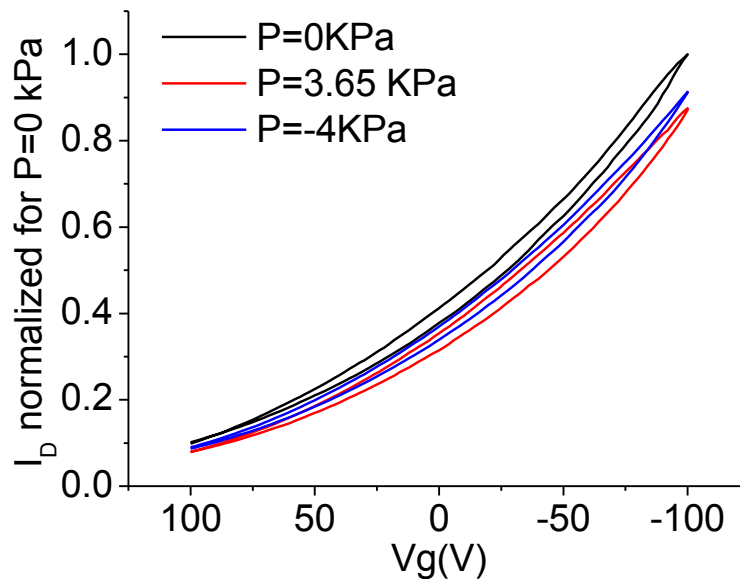
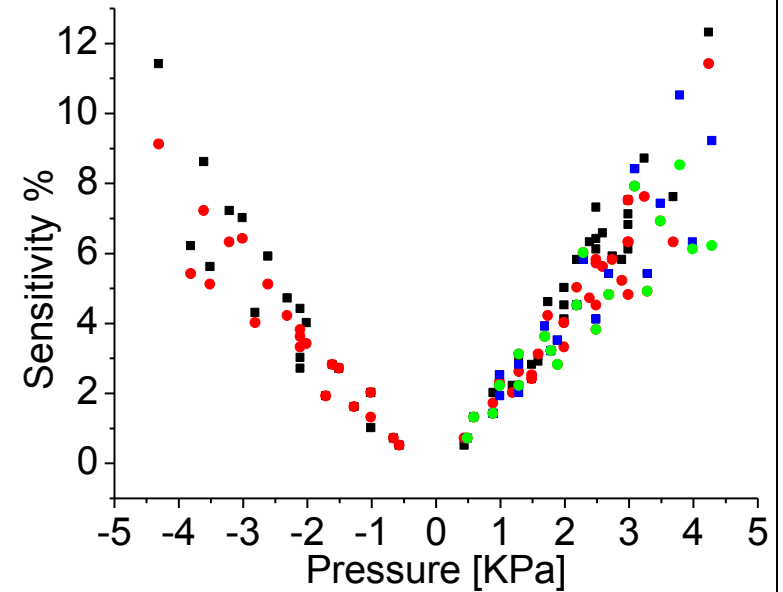
Low sensitivity, around 15%

Response, rise and fall time  $\approx 100\text{ms}$

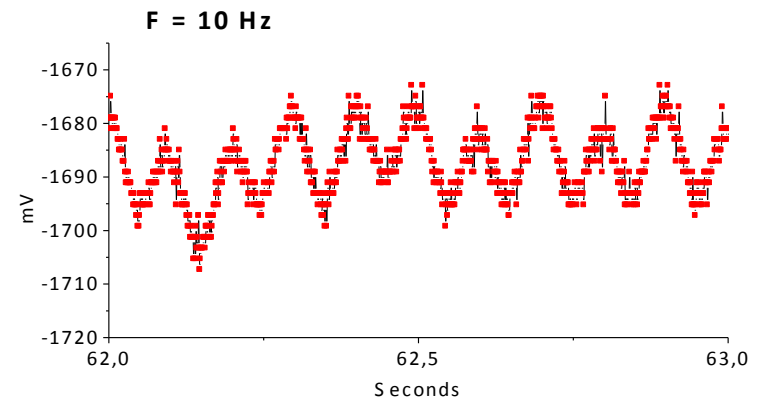
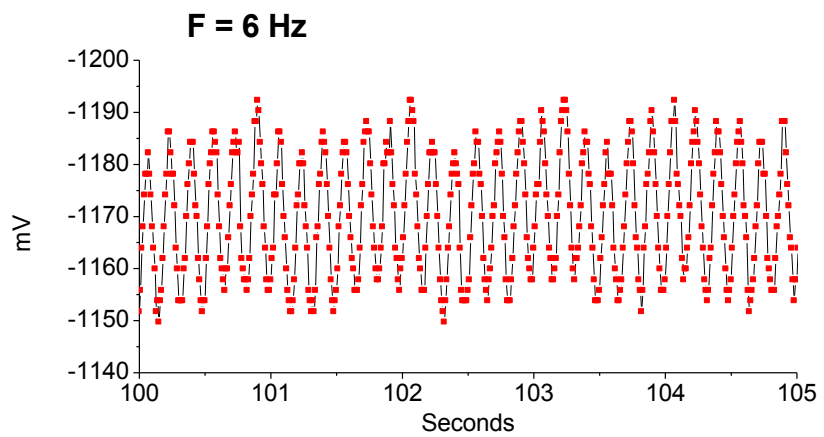
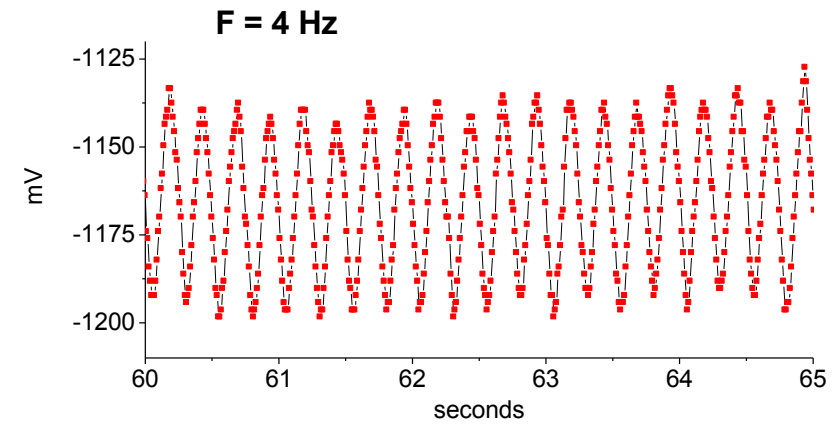
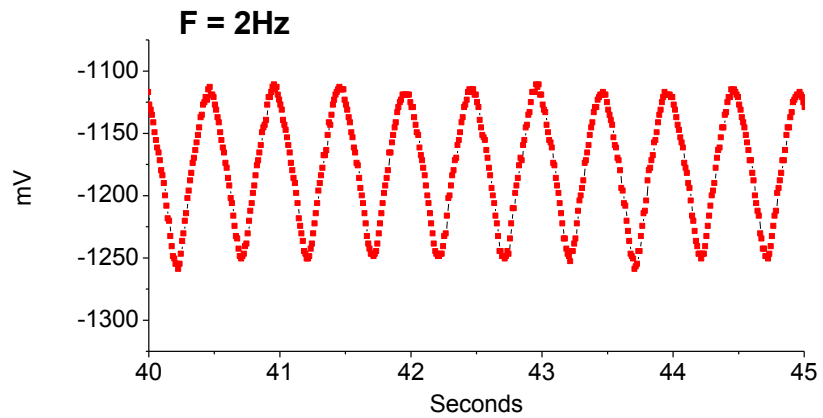
Short TS  $\uparrow$   $>$  around 5-10s

$\downarrow$   $>$  around 5-10s

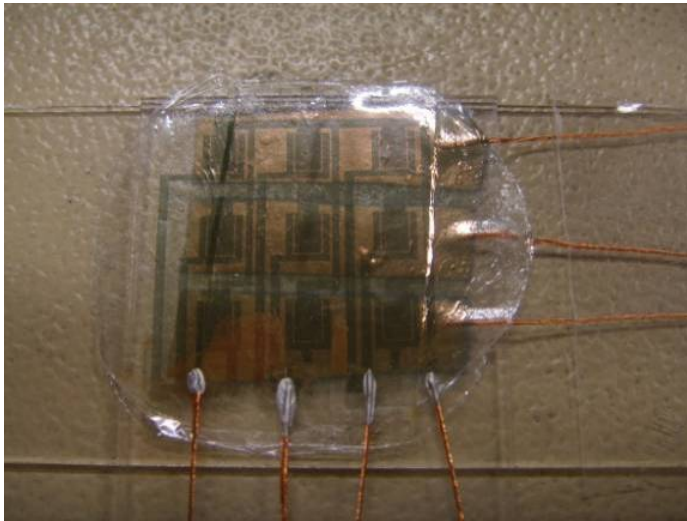
Hysteresis increases for  $P > 2.5\text{kPa}$



# Pressure Sensors: dynamic characterization



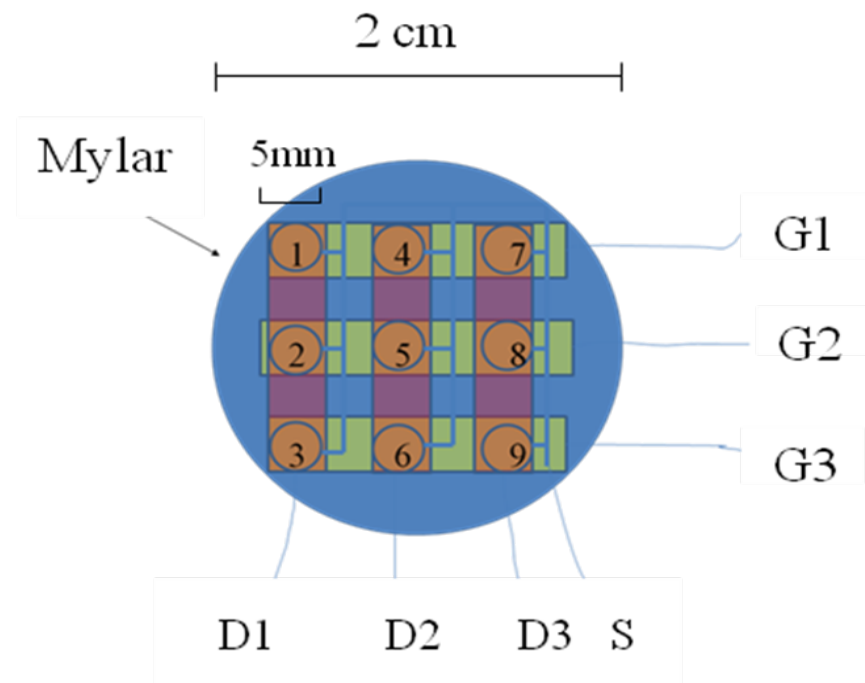
# Some Examples: Matrixes of sensors



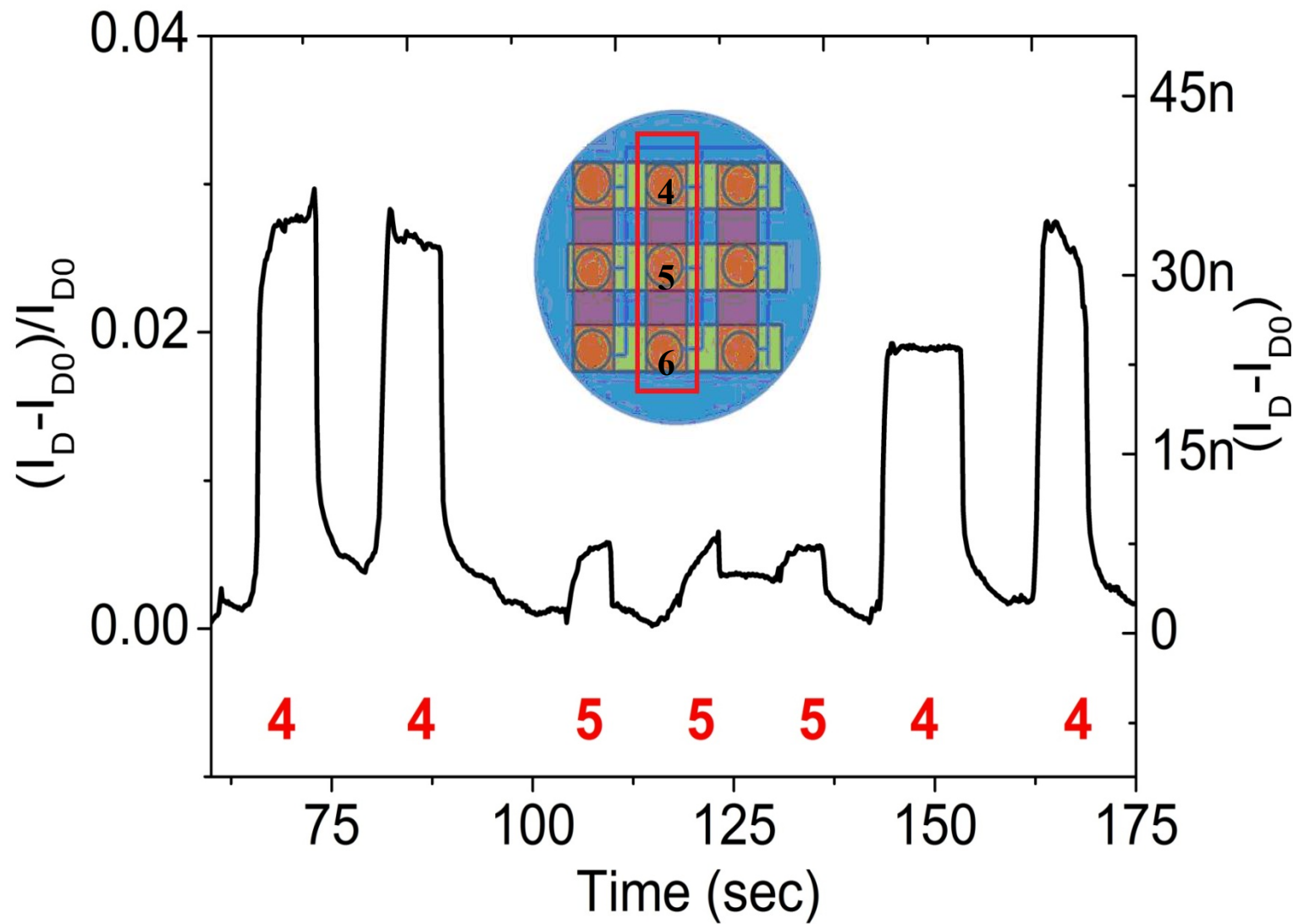
Up to 16 elements in 4cm<sup>2</sup>  
Area  
For pressure distribution  
analyses

Common Ground (Source)  
Rows → Common Gate  
Columns → Common Drain

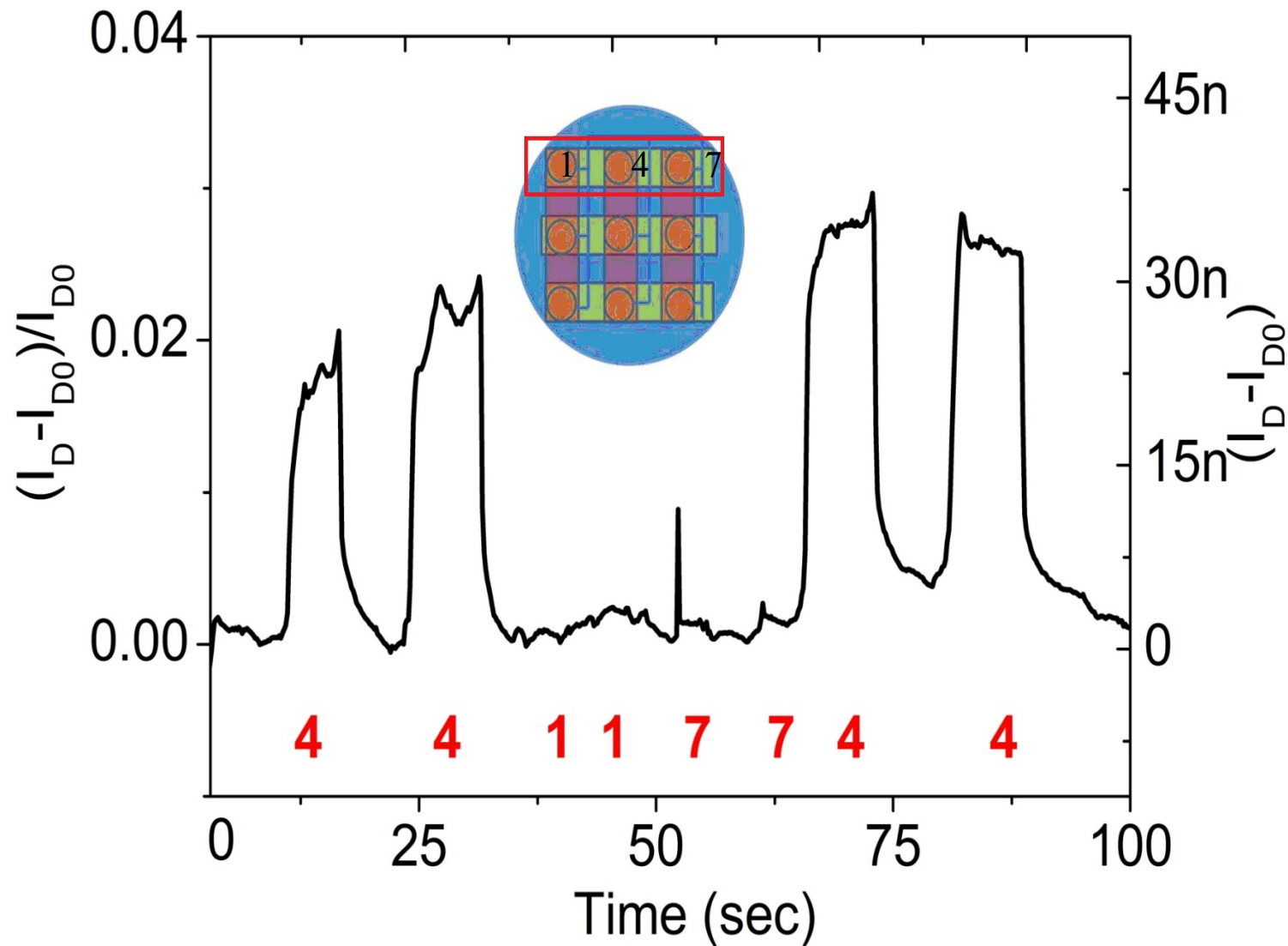
Every single element can be  
independently investigated



# Some Examples: Matrixes of sensors

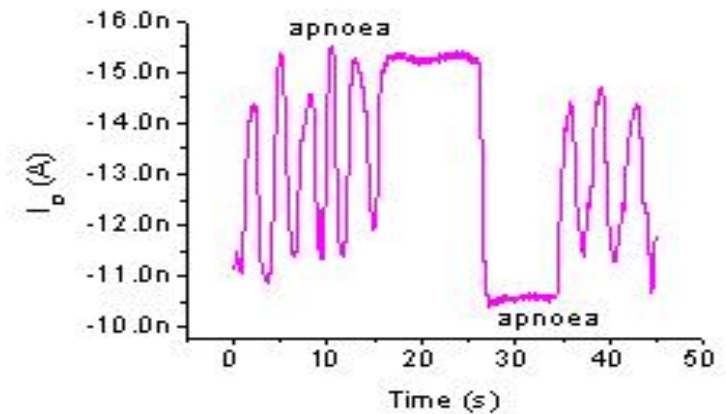


# Some Examples: Matrixes of sensors



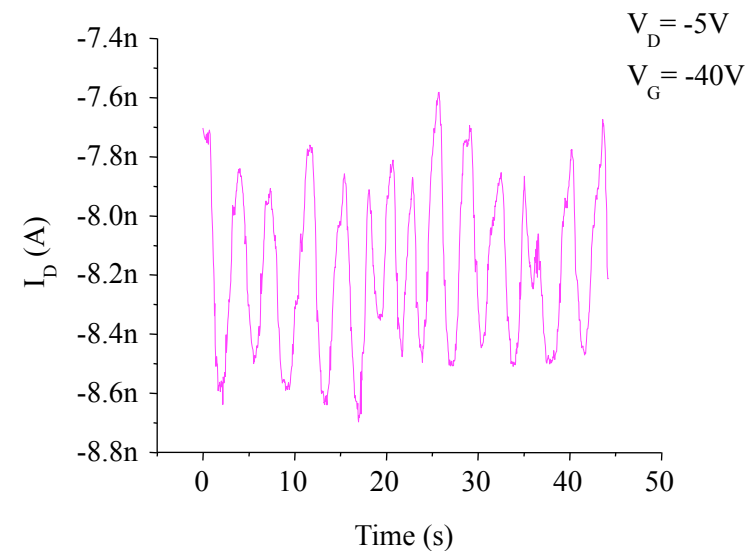
# Some Examples: Breathing monitoring

Sensor applied to a chest bandage for breathing monitoring



(b)

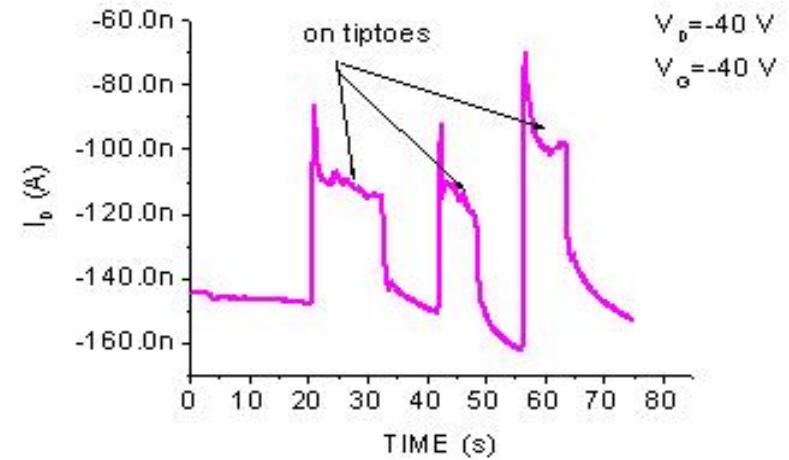
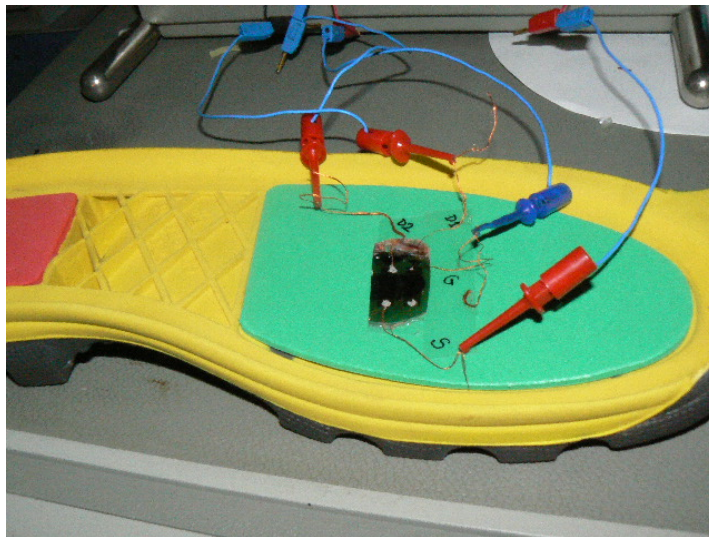
Regular breathing





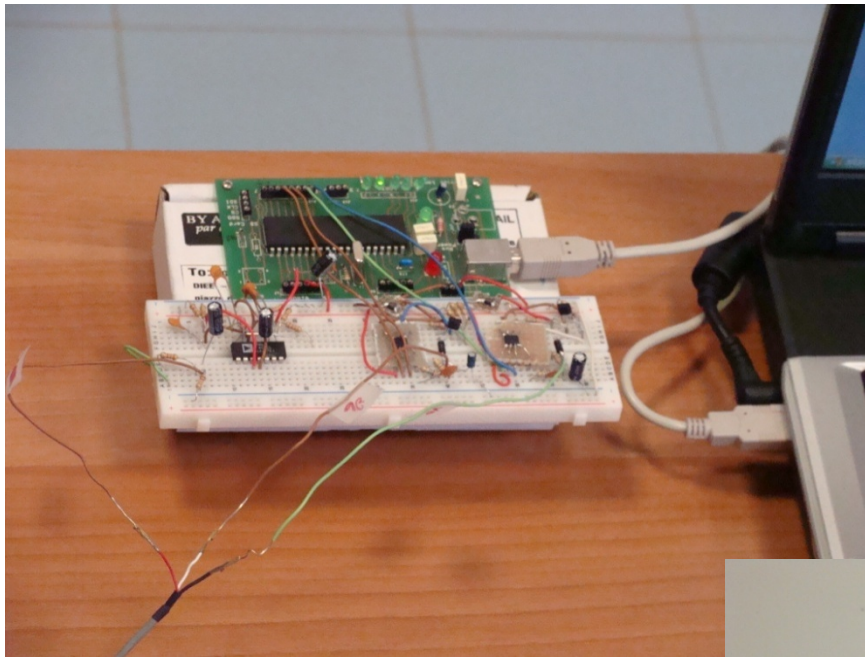
# Some Examples: Posture detection

Sensor applied to a shoe sole for posture detection and monitoring



As can be noticed, output current varies as soon as pressure changes across the active surfaces

# Some Examples: Posture detection

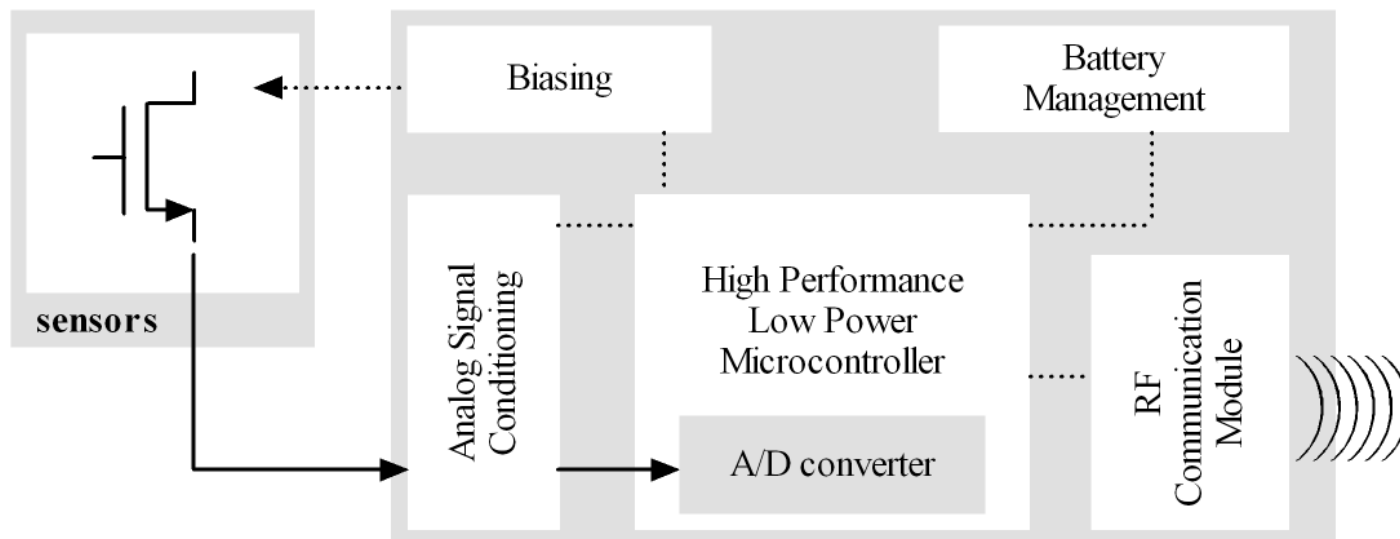
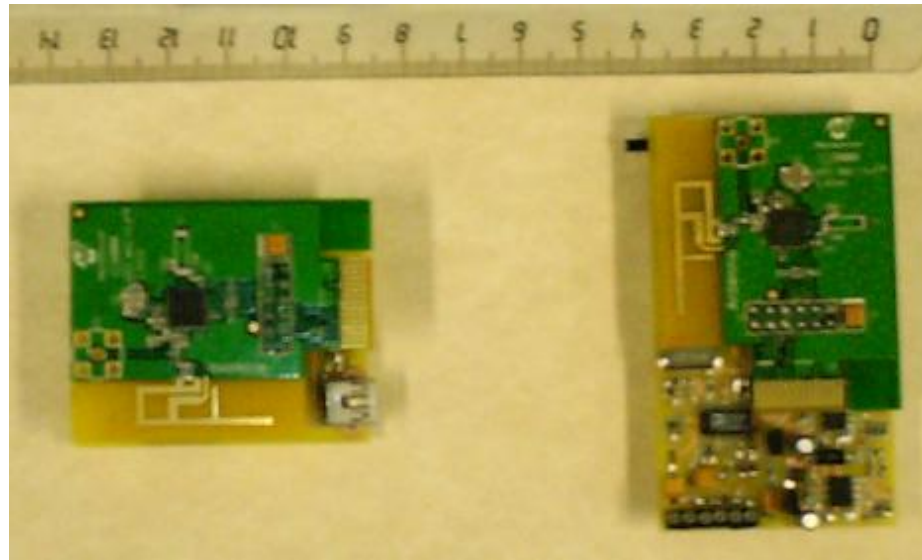


Prototype of the main board and measurement set up



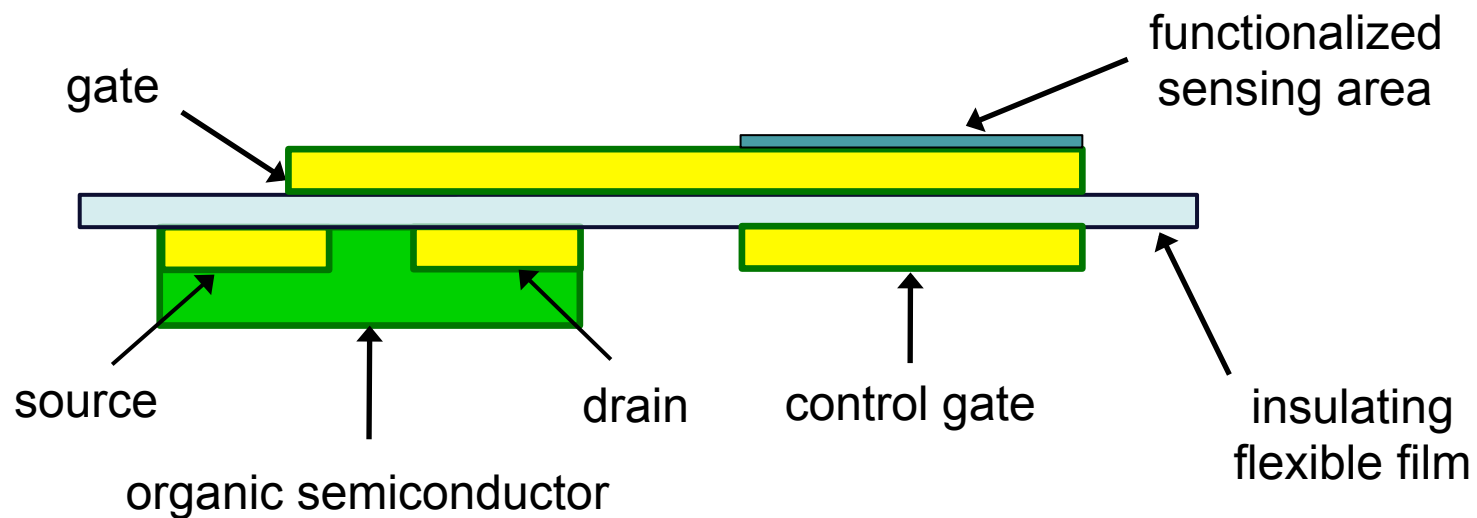


# Some Examples: Posture detection



## Chemical sensors: Device structure

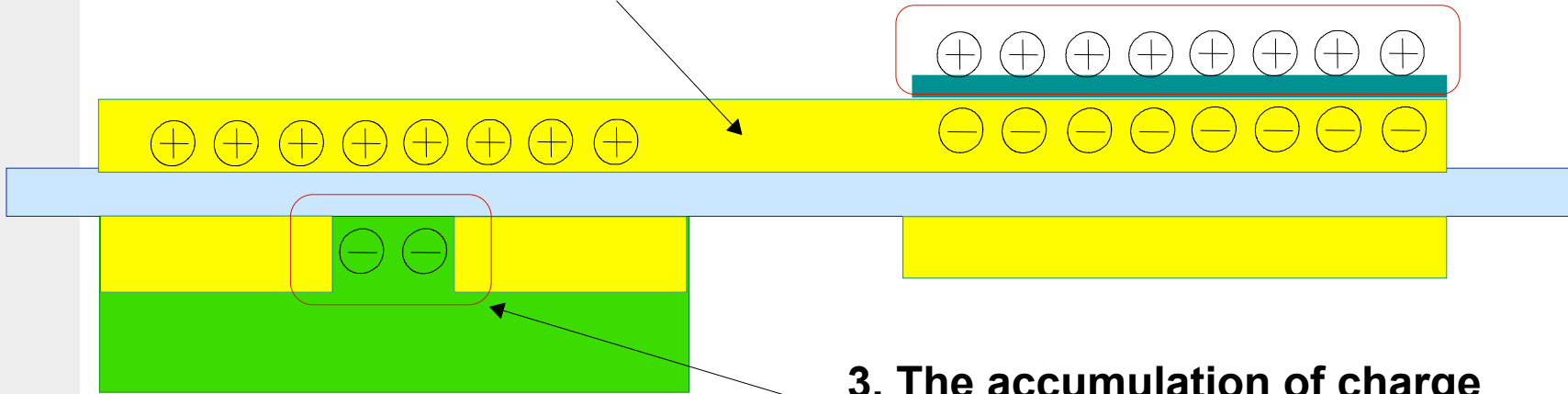
- The sensor structure is based on a fully *flexible organic field-effect transistor* (OFET)
- The device is assembled on a flexible film (Mylar®), which acts as gate insulator



# Working principle

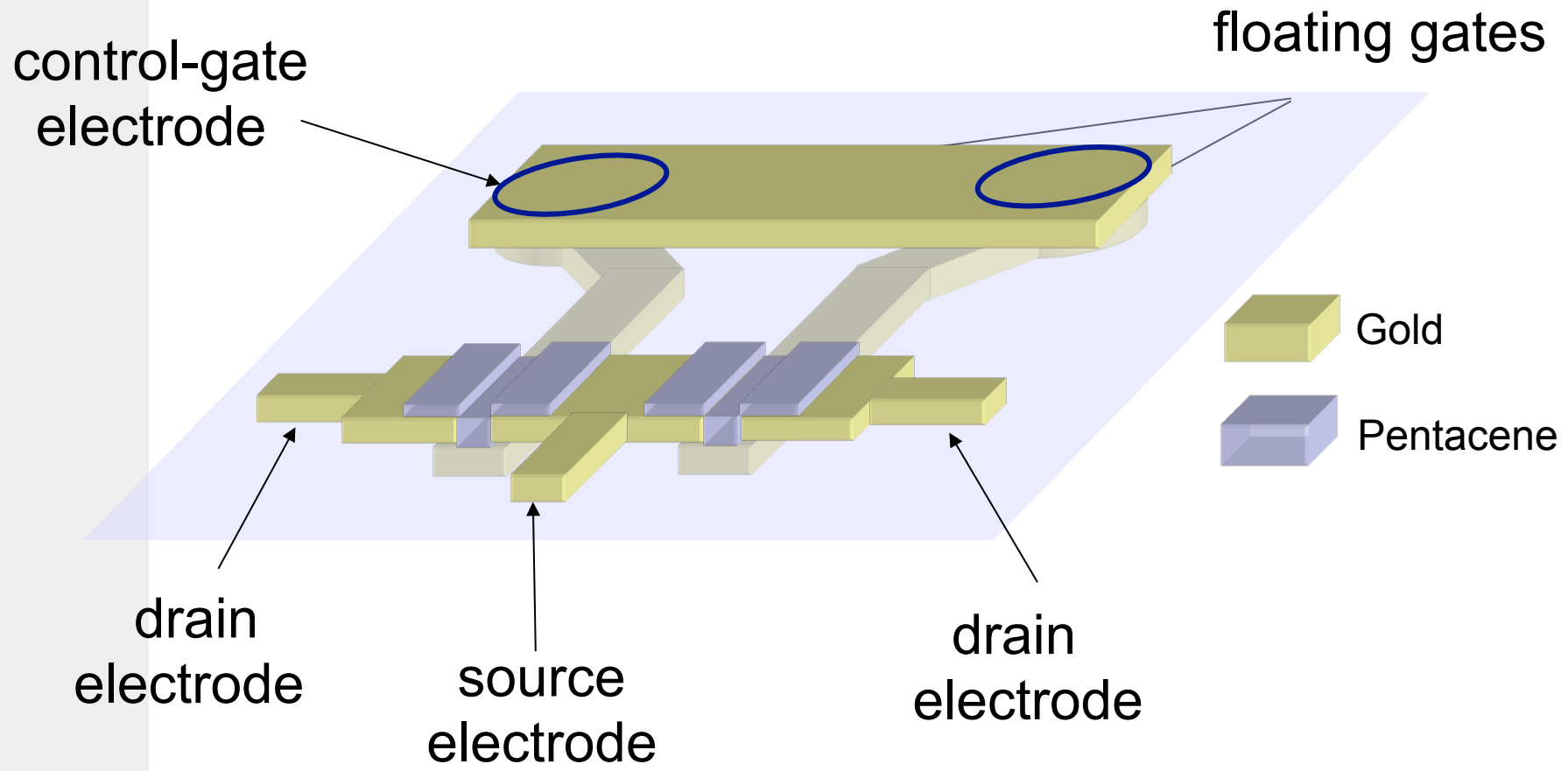
**2. Positive and negative charge separate inside the floating gate**

**1. Electric charge immobilized on the active area**

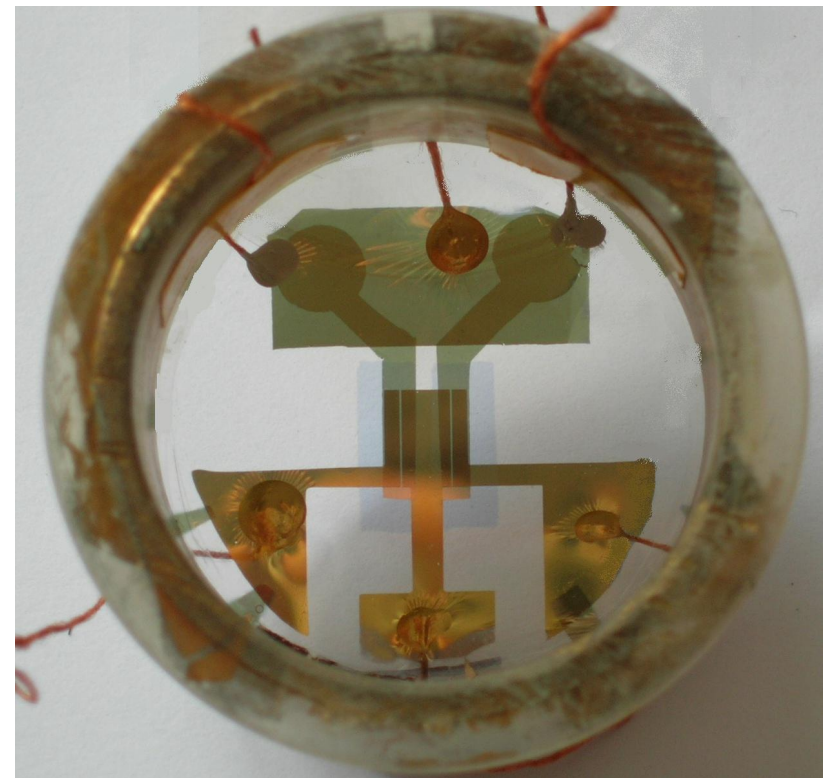
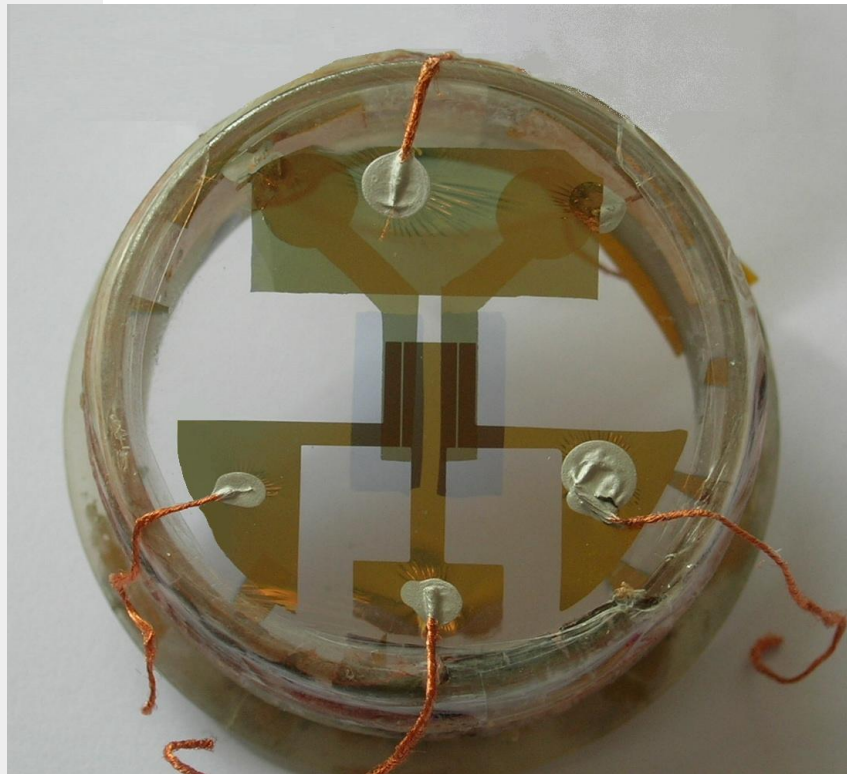


**3. The accumulation of charge affects the channel formation**

# Device processing

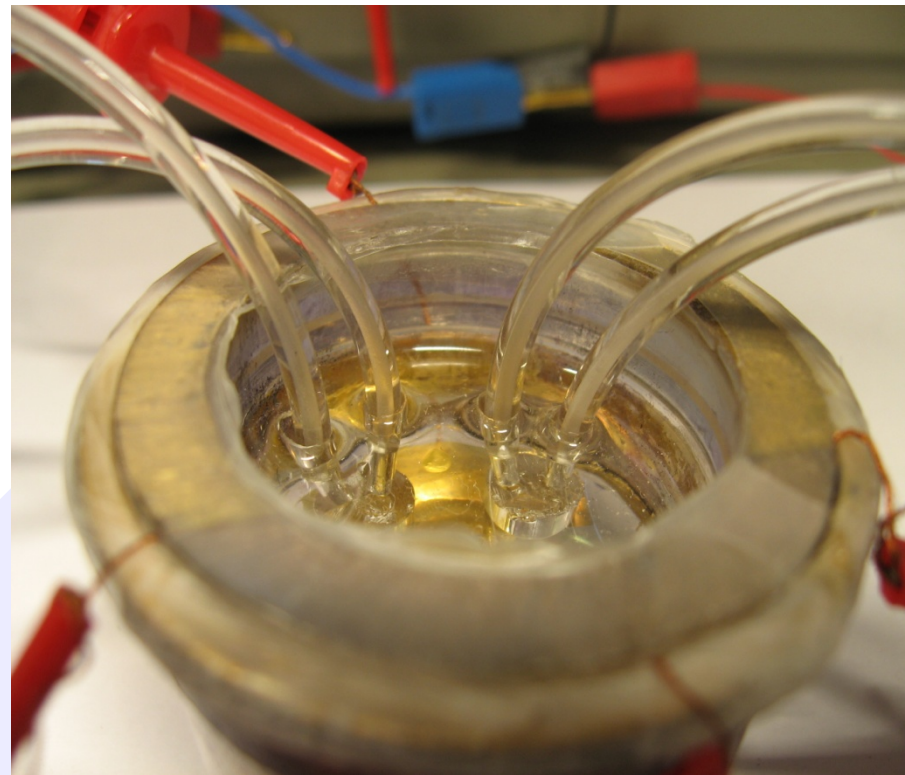


# Fabricated device



# Flow cell

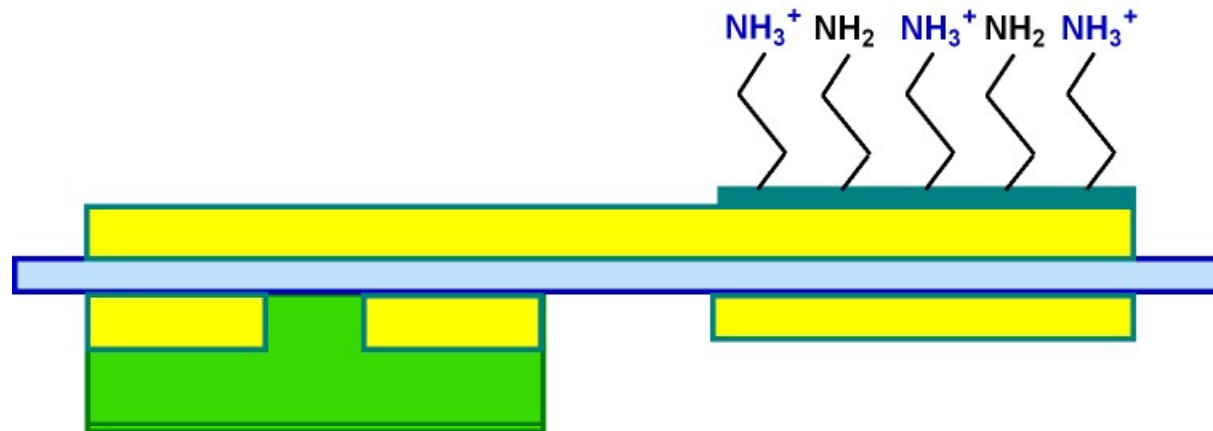
- A *custom flow cell* hosting two chambers with inlet and outlet channels, was developed to handle solutions involved in the assay



Coating gates

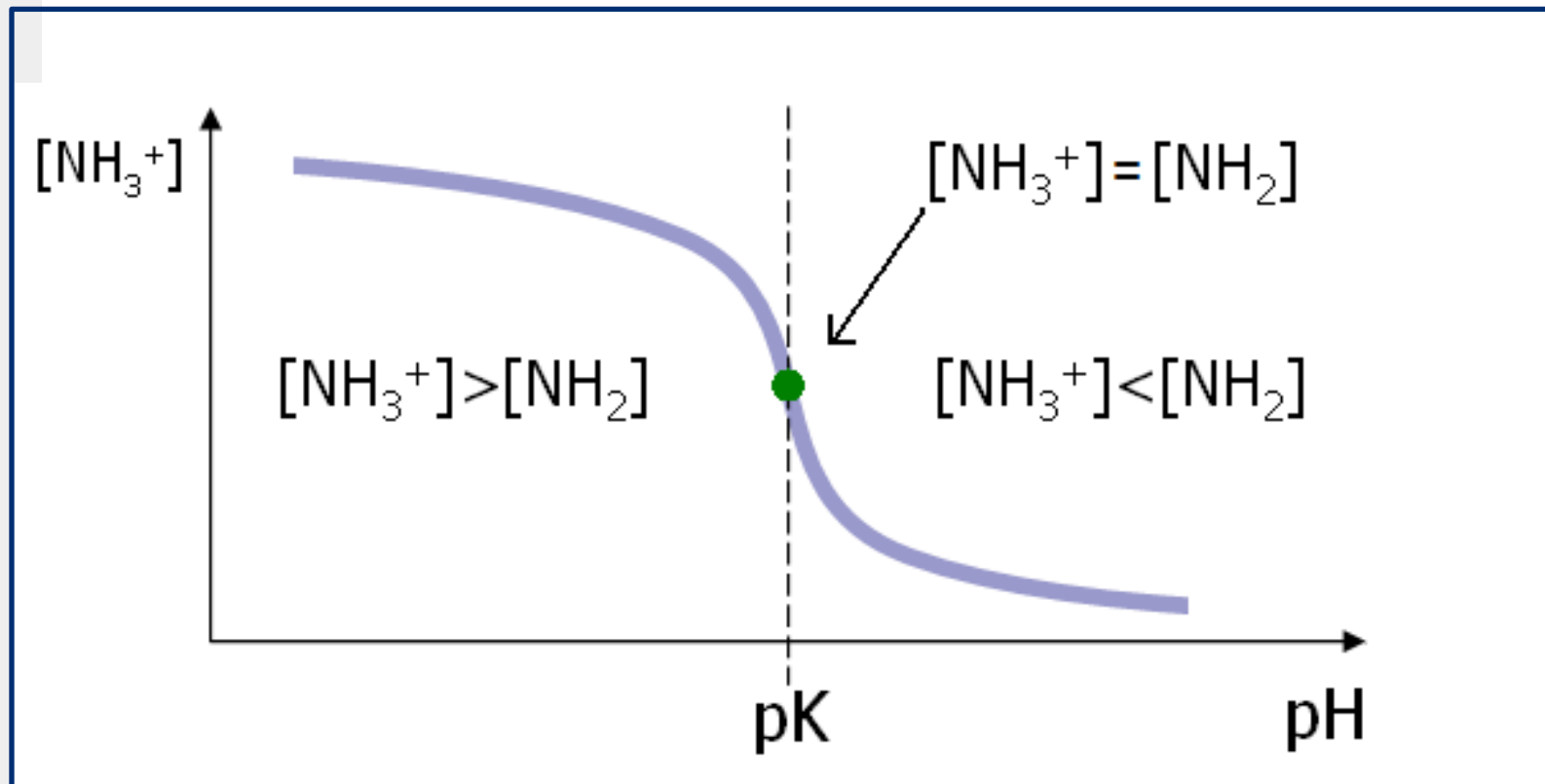
# Ion-sensitive device: functionalization

- The sensitivity is achieved by functionalizing the floating gate by anchoring  $NH_2$  groups on its surface
- The amino groups are mobilized to the sensor upon protonation in proportion to the concentration of  $H^+$  → higher threshold voltage



# Ion-sensitive device: functionalization

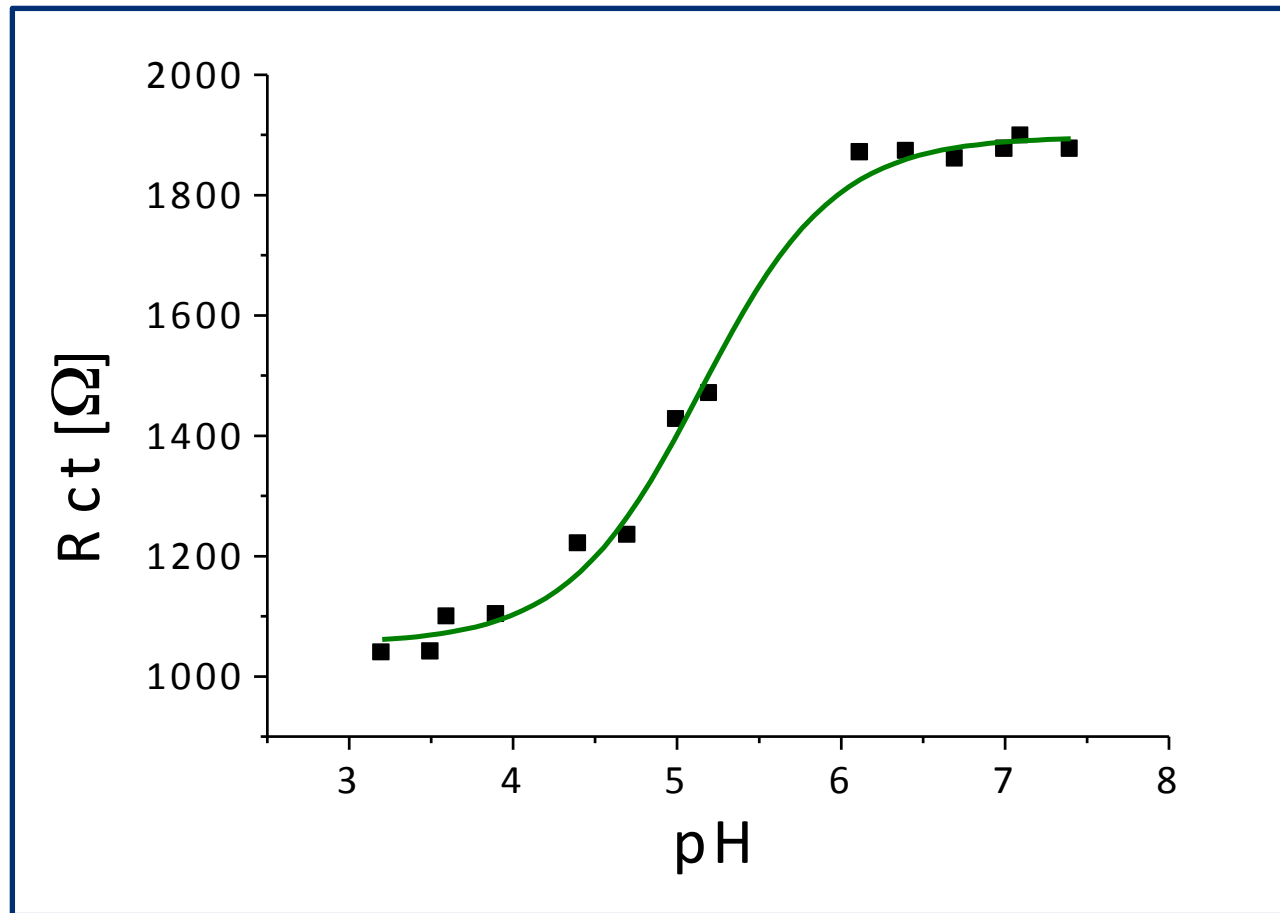
## Amino protonation curve - Graphical representation





# Ion-sensitive device: functionalization

**Amino protonation curve** – *Electrochemical Impedance Spectroscopy (EIS) measurements*

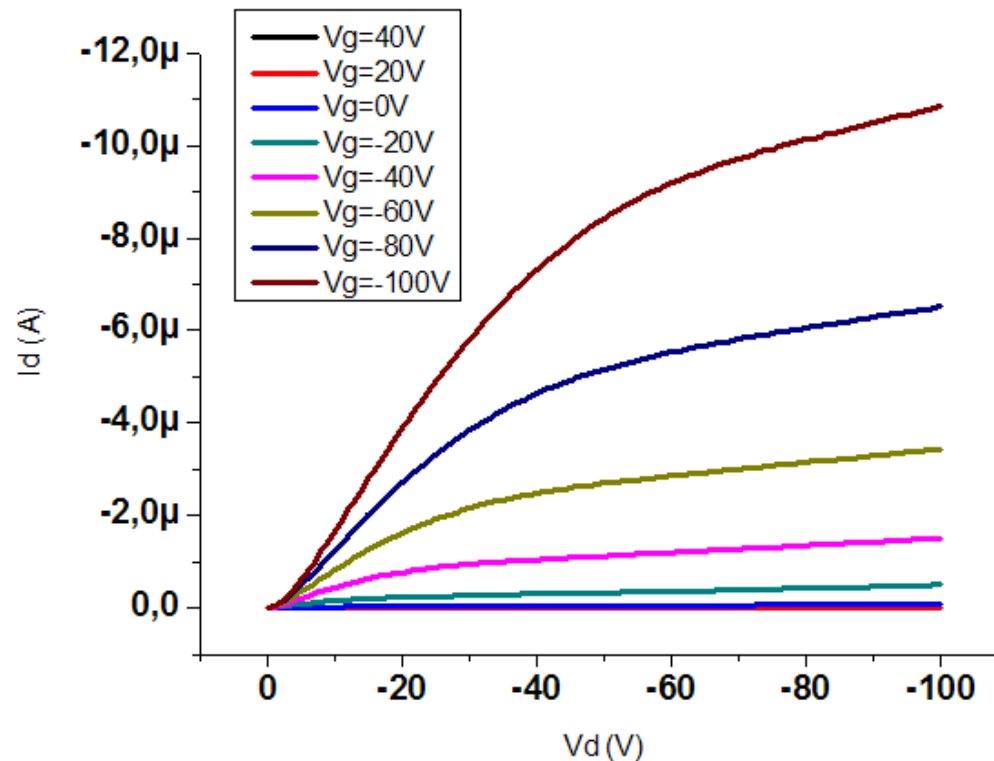


# Ion-sensitive device: experimental results

- The device has the typical behavior of an organic *p-type* field effect transistor, working in accumulation

- The ion-sensitivity is demonstrated by the change in the drain current

- The test solution is a custom-developed nitrate system

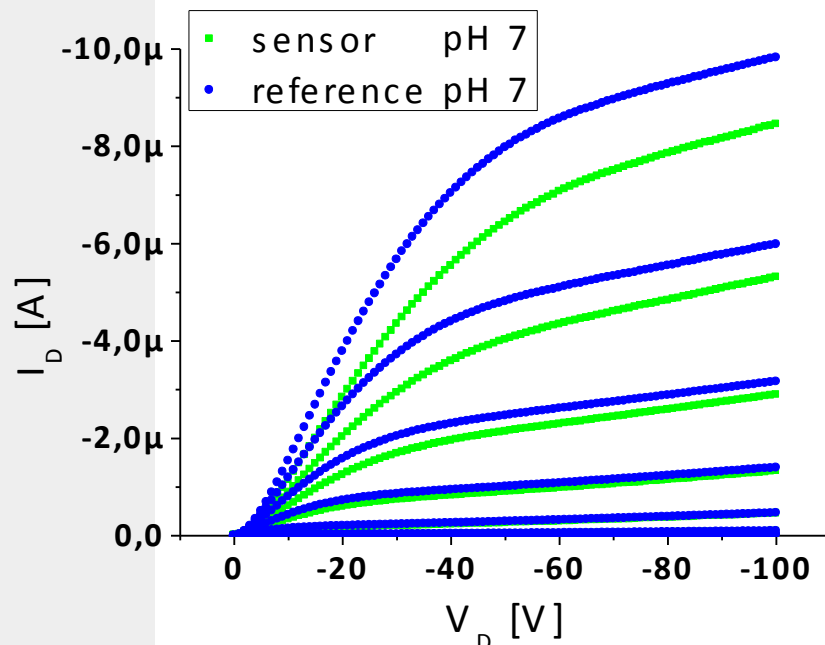


ring the induced by lution

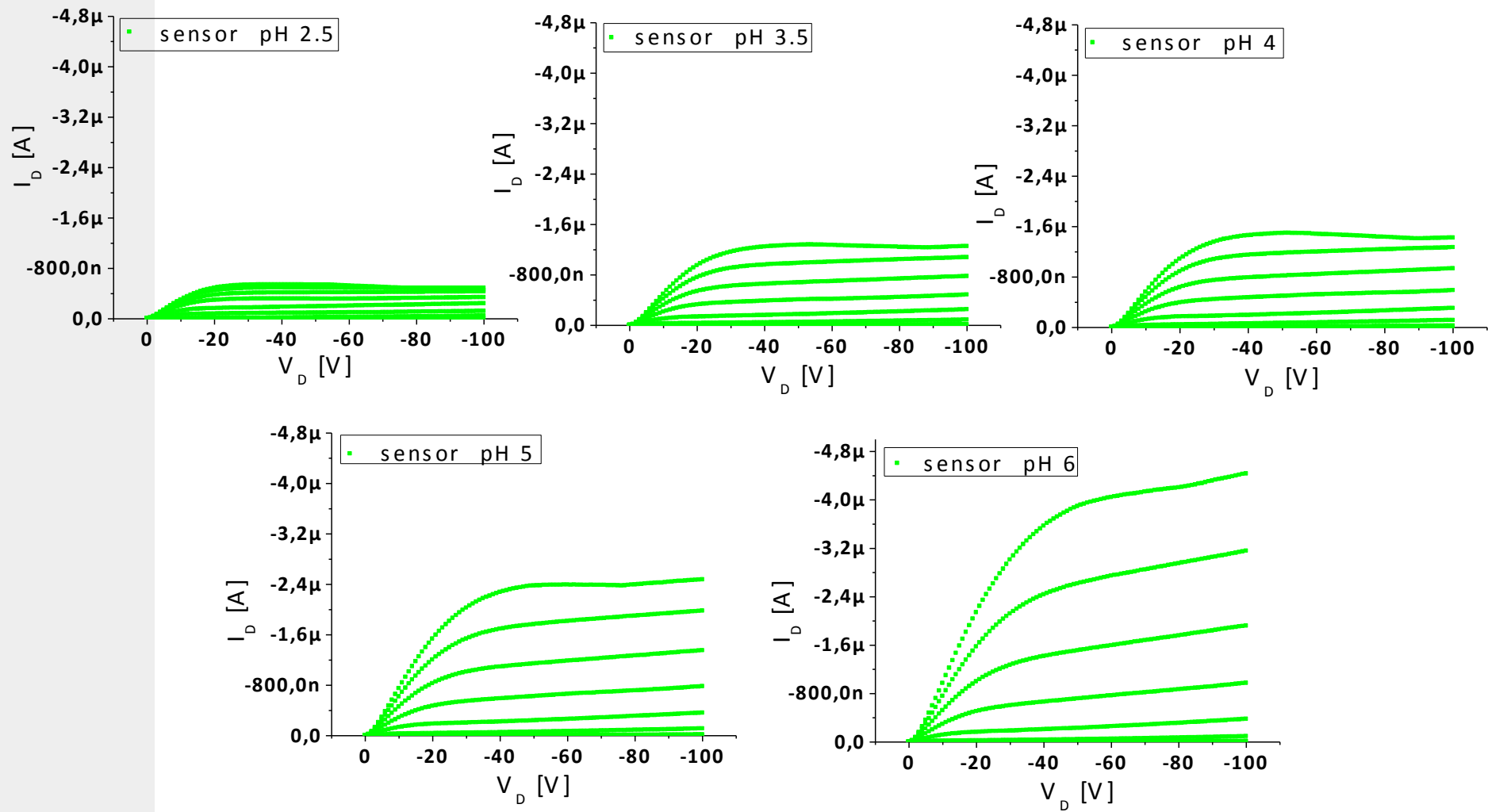
cing the is of the

## Ion-sensitive device: experimental results

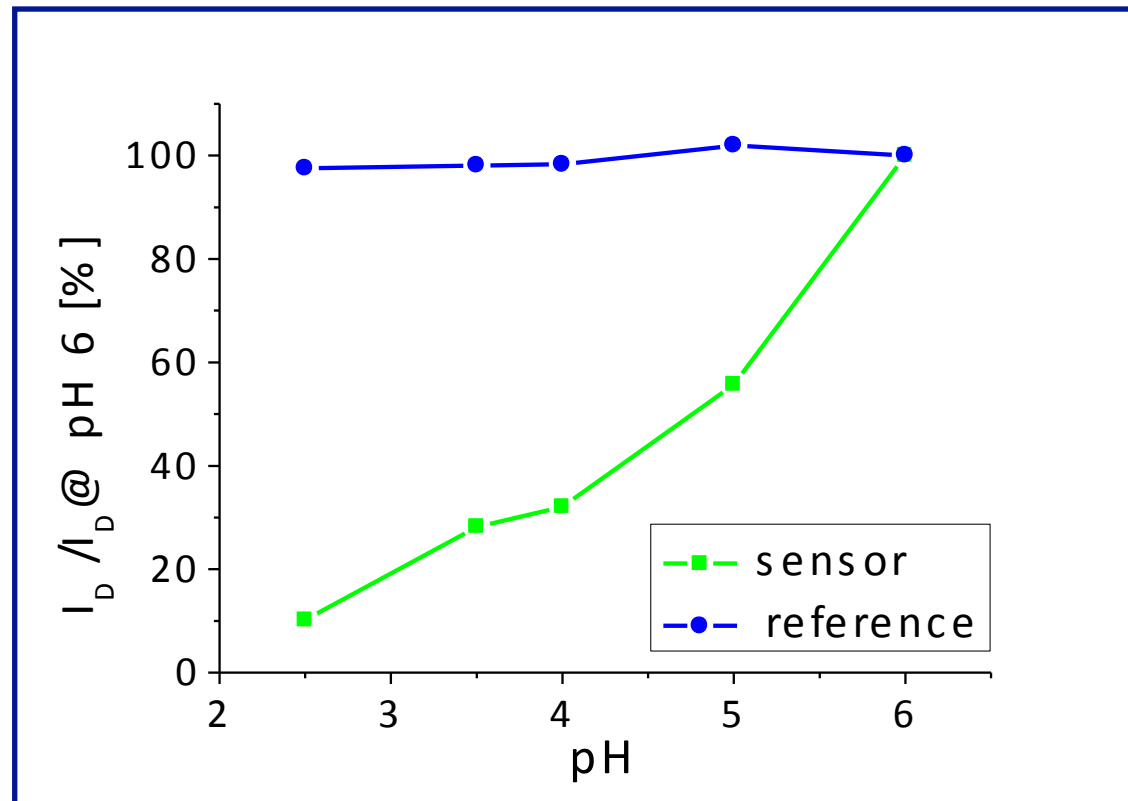
- The testing was performed by placing solutions at different pH values on the sensor, while keeping a solution at pH 7 on the reference



# Ion-sensitive device: experimental results

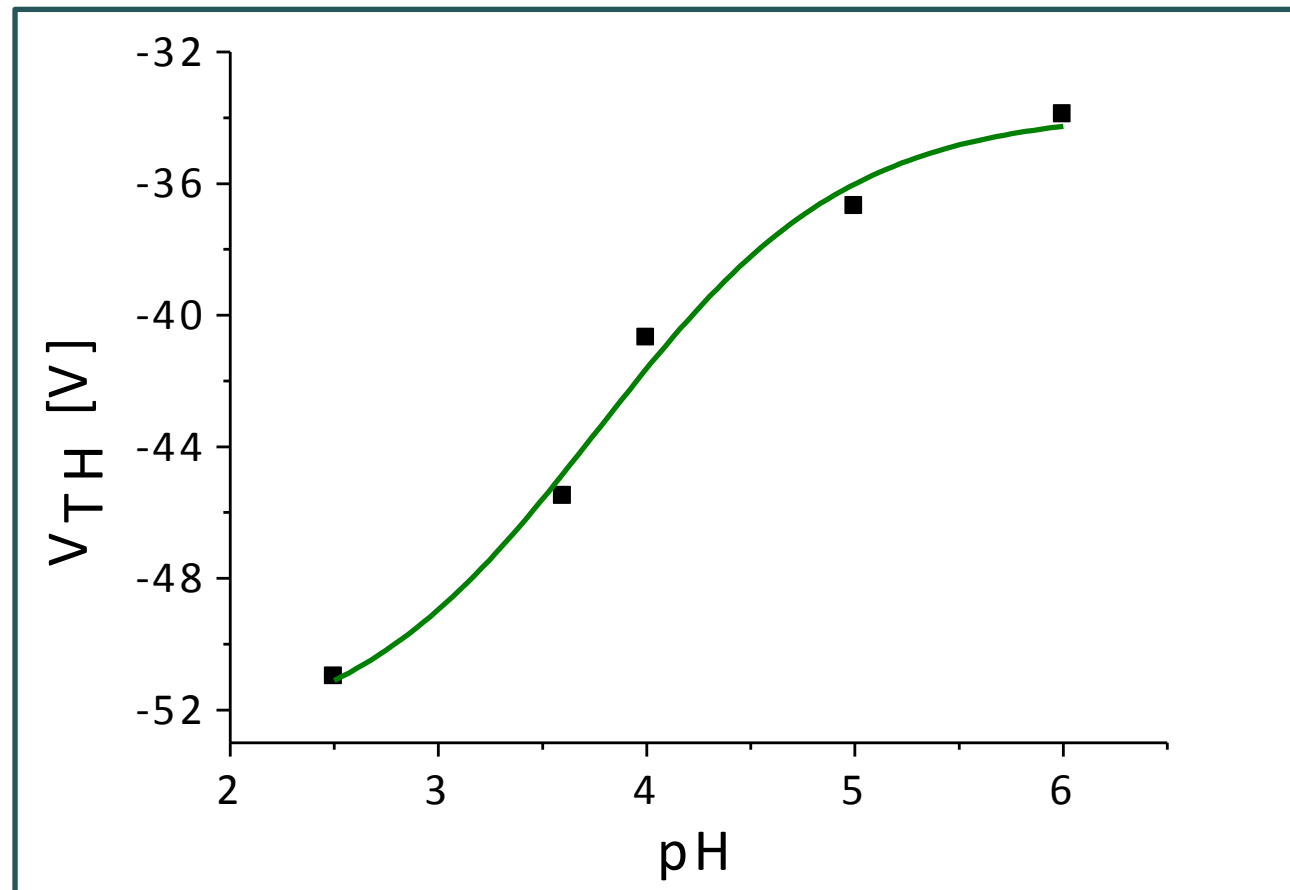


## Ion-sensitive device: experimental results



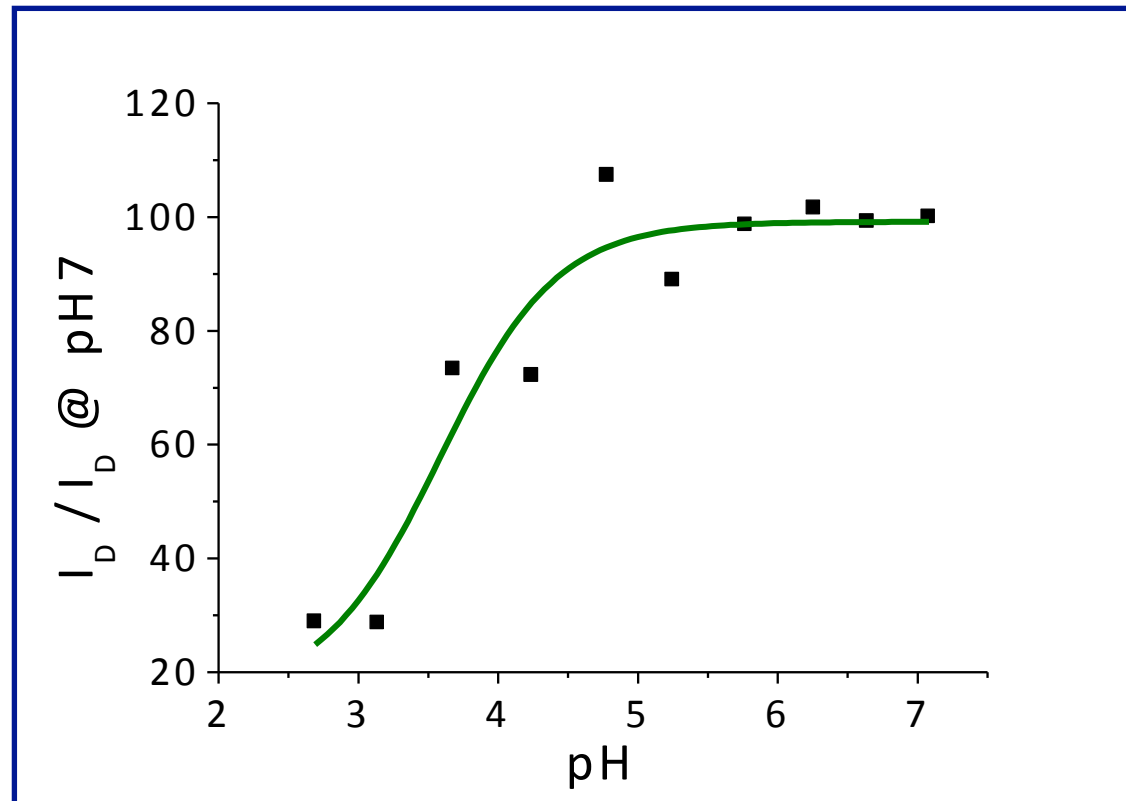
- Maximum *drain current* measured on both the sensor and the reference with varying pH (currents values normalized with reference to the current at pH 6)

## Ion-sensitive device: experimental results



- Variation of the effective *threshold voltage* of the sensor with varying pH of the solution

## Ion-sensitive device: experimental results



- Trend of the maximum sensor drain current with varying the pH towards more acid solutions

# Conclusions: OFETs based sensors perspectives

- Electronic skin
- Biomedicine
  - Physiological parameter monitoring
- Smart textiles
- Wearable electronics

